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Park et al.

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(54) **ORGANIC LIGHT EMITTING DISPLAY
DEVICE AND METHOD FOR
MANUFACTURING THE SAME**

H01L 51/508; H01L 51/5004; H01L
51/0097; H01L 27/3248; H01L 27/322;
H01L 27/3246; H01L 51/001

See application file for complete search history.

(71) Applicant: **LG Display Co., Ltd.**, Seoul (KR)

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(72) Inventors: **TaeHan Park**, Seoul (KR);
KyungHoon Lee, Goyangi-si (KR);
DongHee Yoo, Seoul (KR); **Hyeongjun
Lim**, Seoul (KR)

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(73) Assignee: **LG Display Co., Ltd.**, Seoul (KR)

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U.S.C. 154(b) by 0 days.

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Primary Examiner — Donald L Raleigh

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(74) *Attorney, Agent, or Firm* — Fenwick & West LLP

(30) **Foreign Application Priority Data**

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(57) **ABSTRACT**

(51) **Int. Cl.**
H01L 51/52 (2006.01)
H01L 51/50 (2006.01)

(Continued)

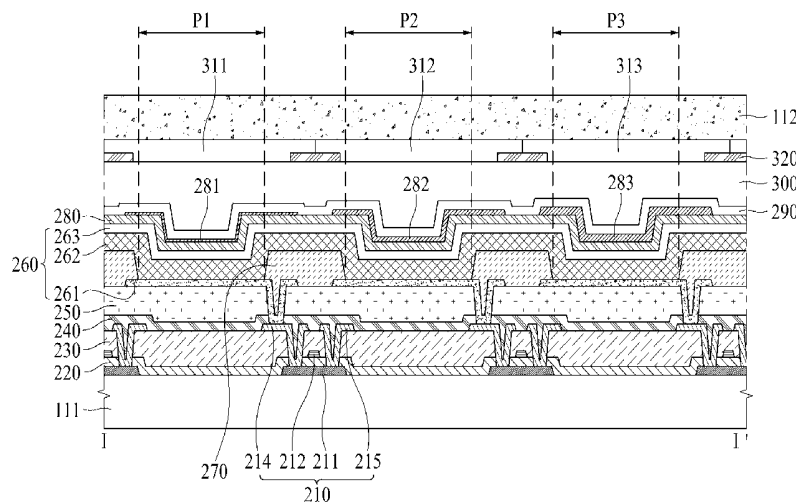
Disclosed is an OLED device capable of reducing the number of manufacturing processes to apply a micro-cavity structure, and a method for manufacturing the same, wherein the OLED device may include a pixel having first to third subpixels, wherein each of the first to third subpixels includes a first electrode including a reflective metal material, an organic light emitting layer on the first electrode, a second electrode disposed on the organic light emitting layer and formed of a transparent metal material, and a semi-transmissive electrode on the second electrode, wherein a distance between the first electrode and the semi-transmissive electrode in the first subpixel, a distance between the first electrode and the semi-transmissive electrode in the second subpixel, and a distance between the first electrode and the semi-transmissive electrode in the third subpixel are different from one another.

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27/3246 (2013.01); **H01L 27/3248** (2013.01);
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(2013.01); **H01L 51/50** (2013.01);
(Continued)

(58) **Field of Classification Search**

CPC . H01L 51/5076; H01L 51/5256; H01L 51/56;

19 Claims, 32 Drawing Sheets



- (51) **Int. Cl.**
H01L 27/32 (2006.01)
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- (52) **U.S. Cl.**
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(2013.01); **H01L 51/5225** (2013.01); **H01L**
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H01L 51/5265 (2013.01); **H01L 51/56**
(2013.01); **H01L 2251/558** (2013.01)

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FIG. 1

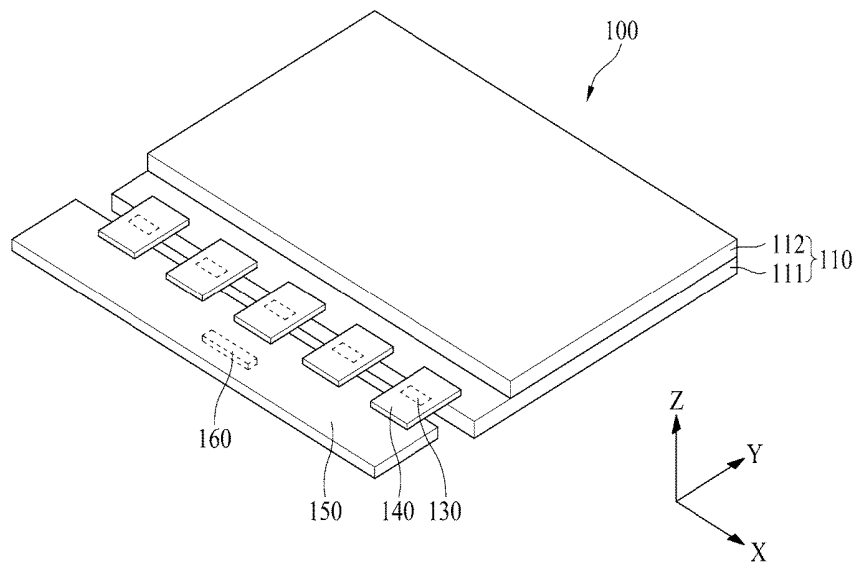


FIG. 2

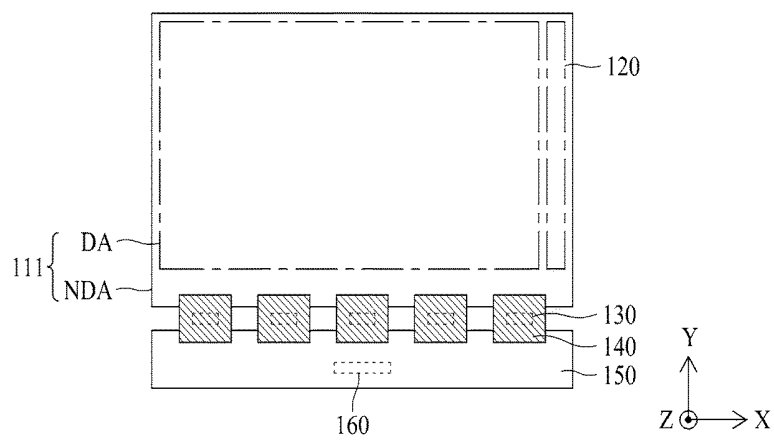


FIG. 3

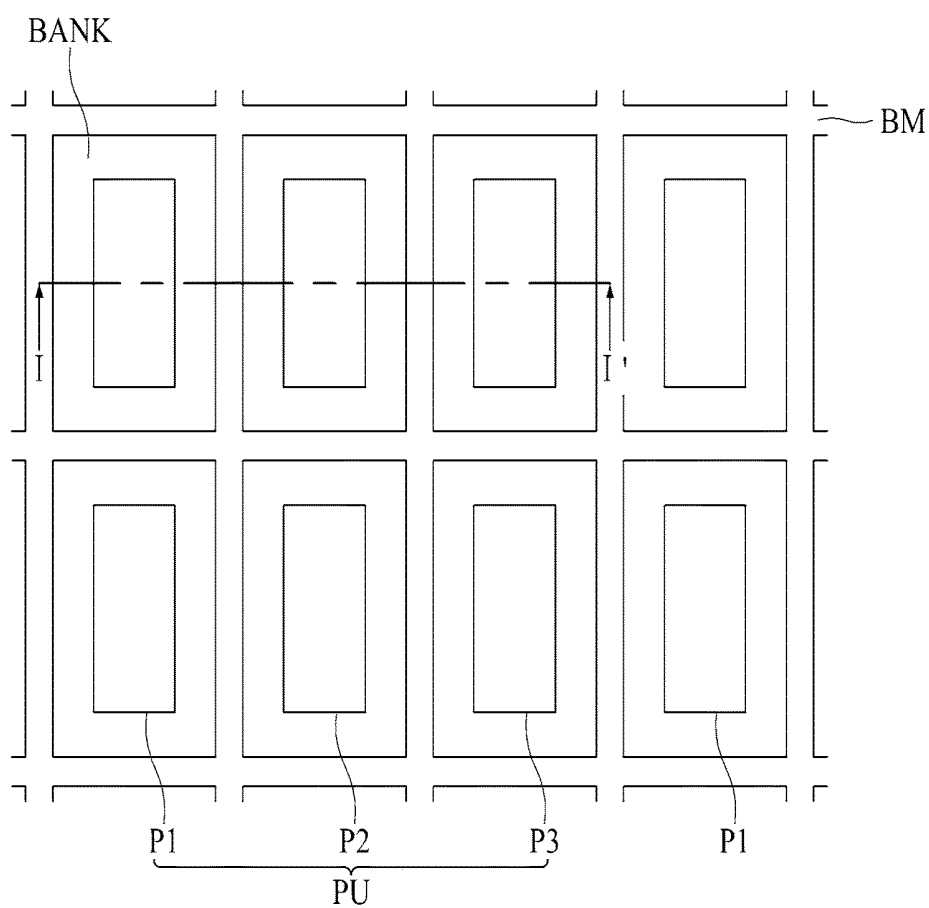


FIG. 4

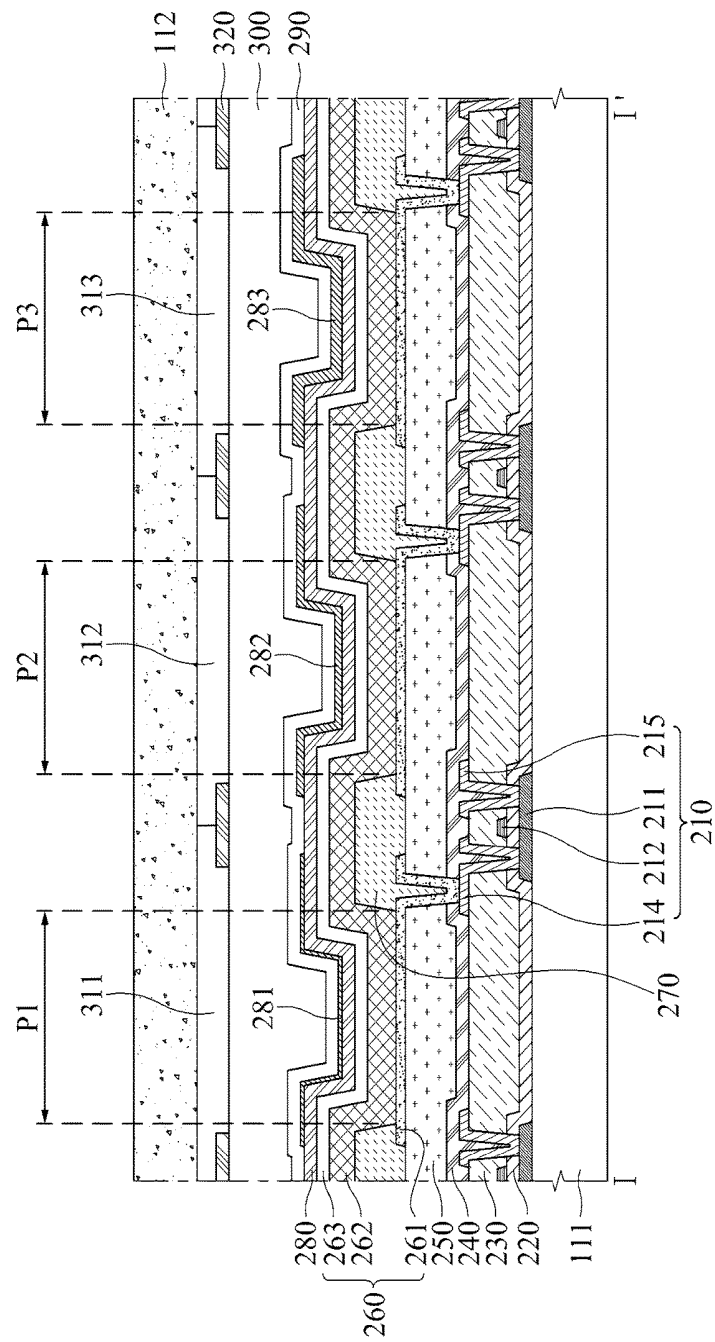


FIG. 5

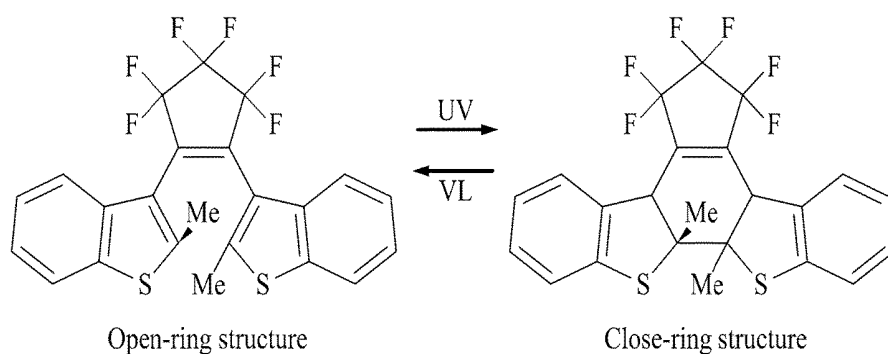


FIG. 6

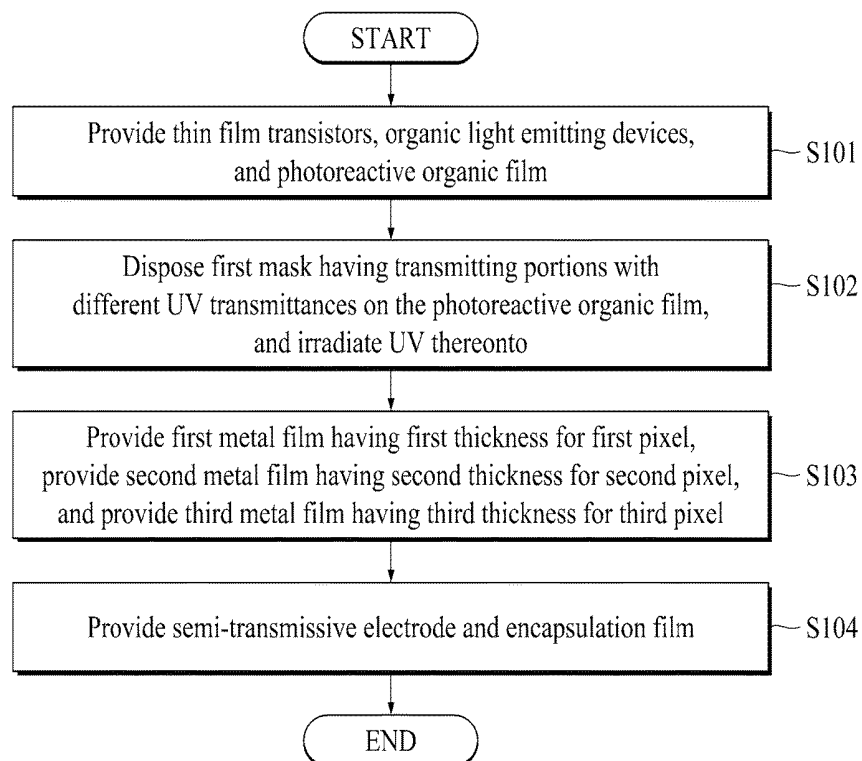


FIG. 7A

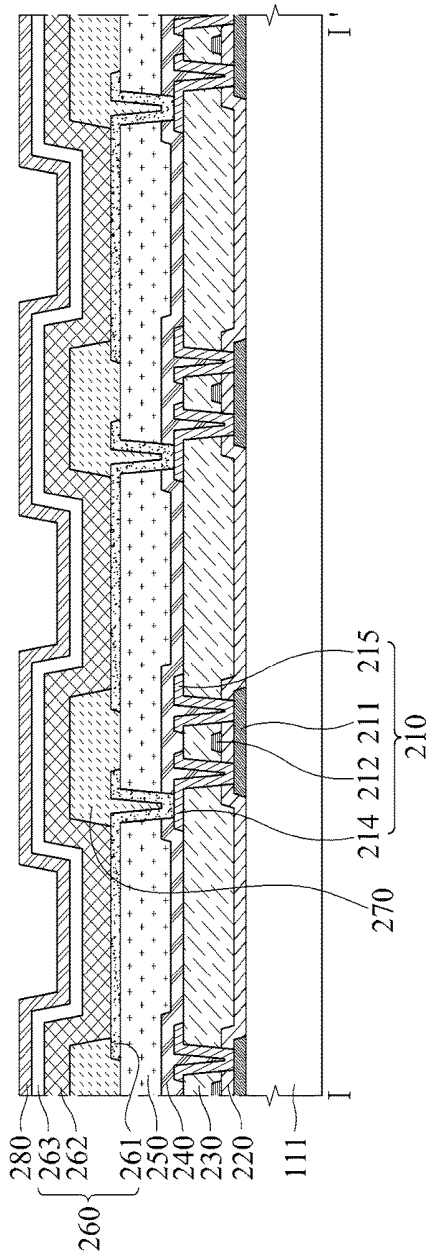


FIG. 7B

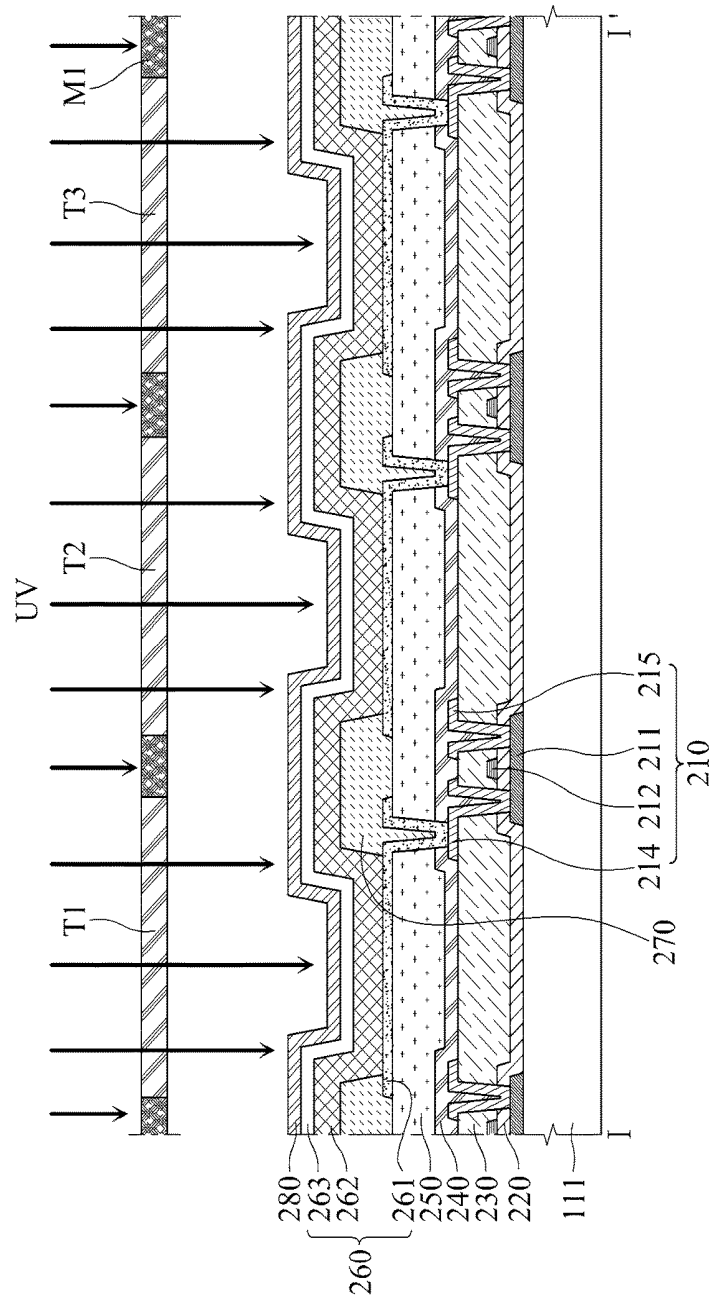


FIG. 7C

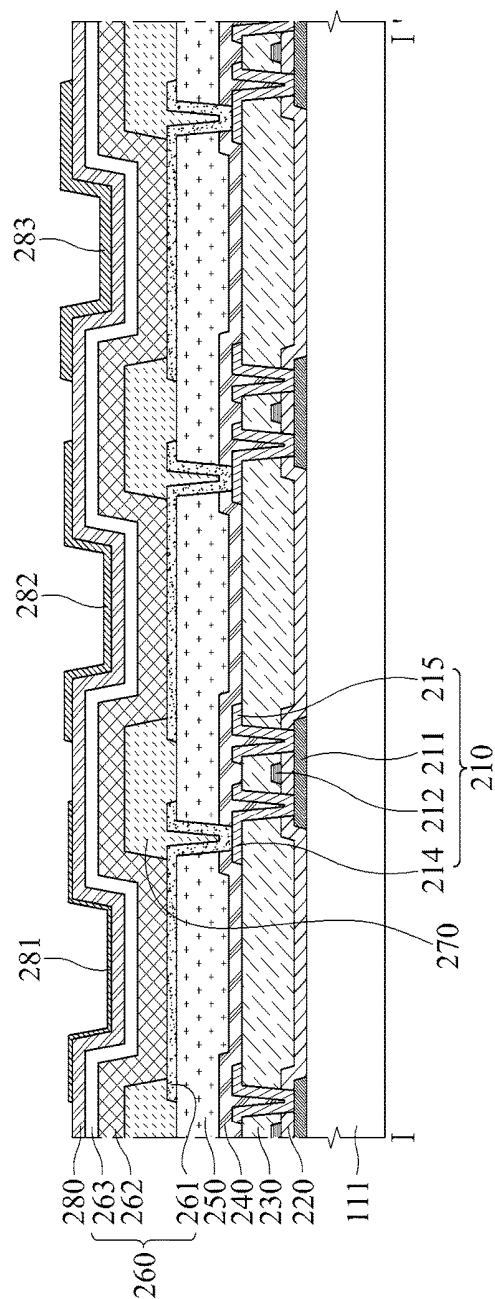


FIG. 7D

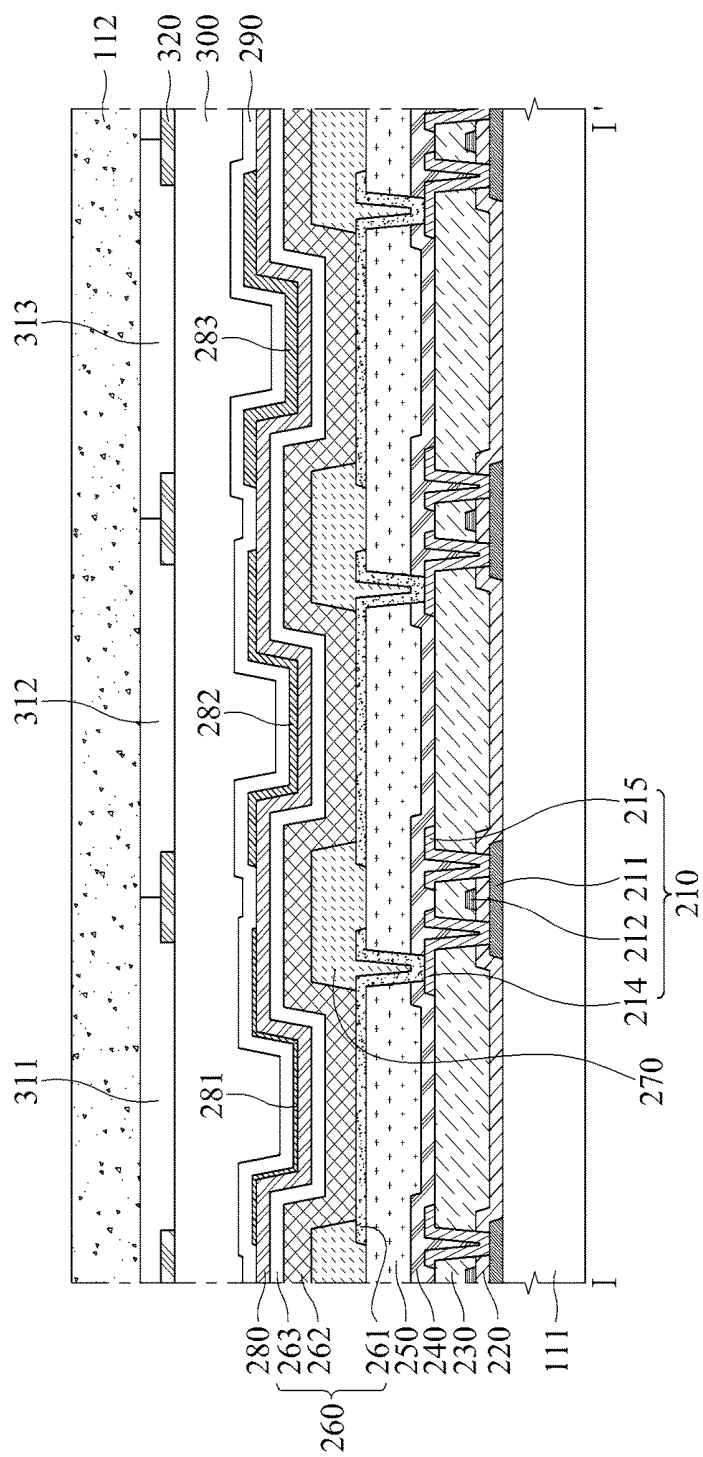


FIG. 8

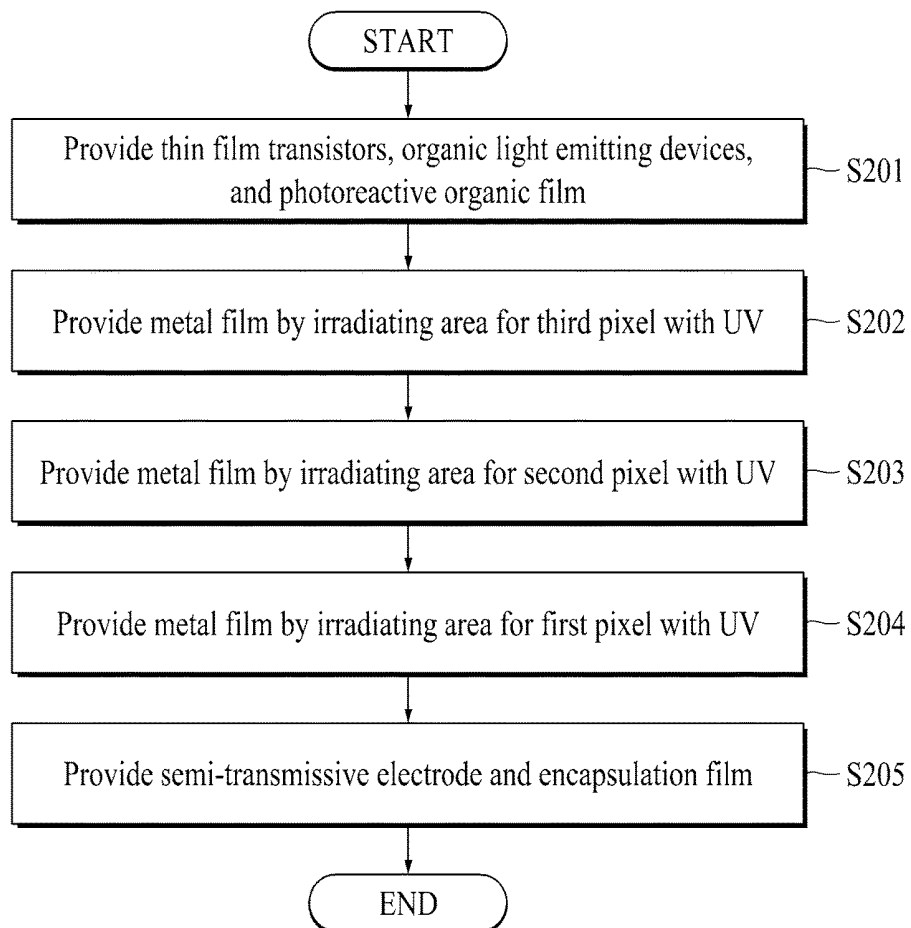


FIG. 9A

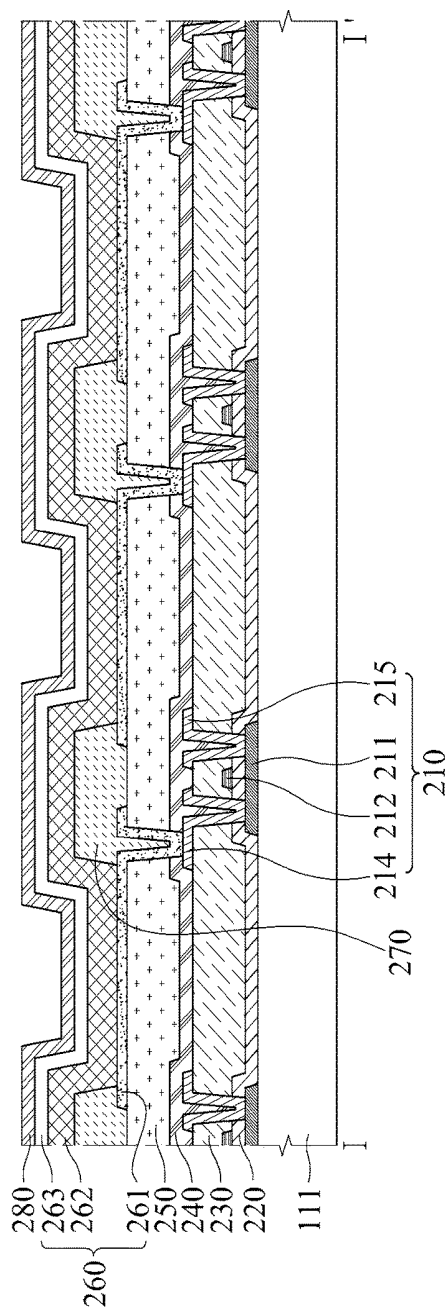


FIG. 9B

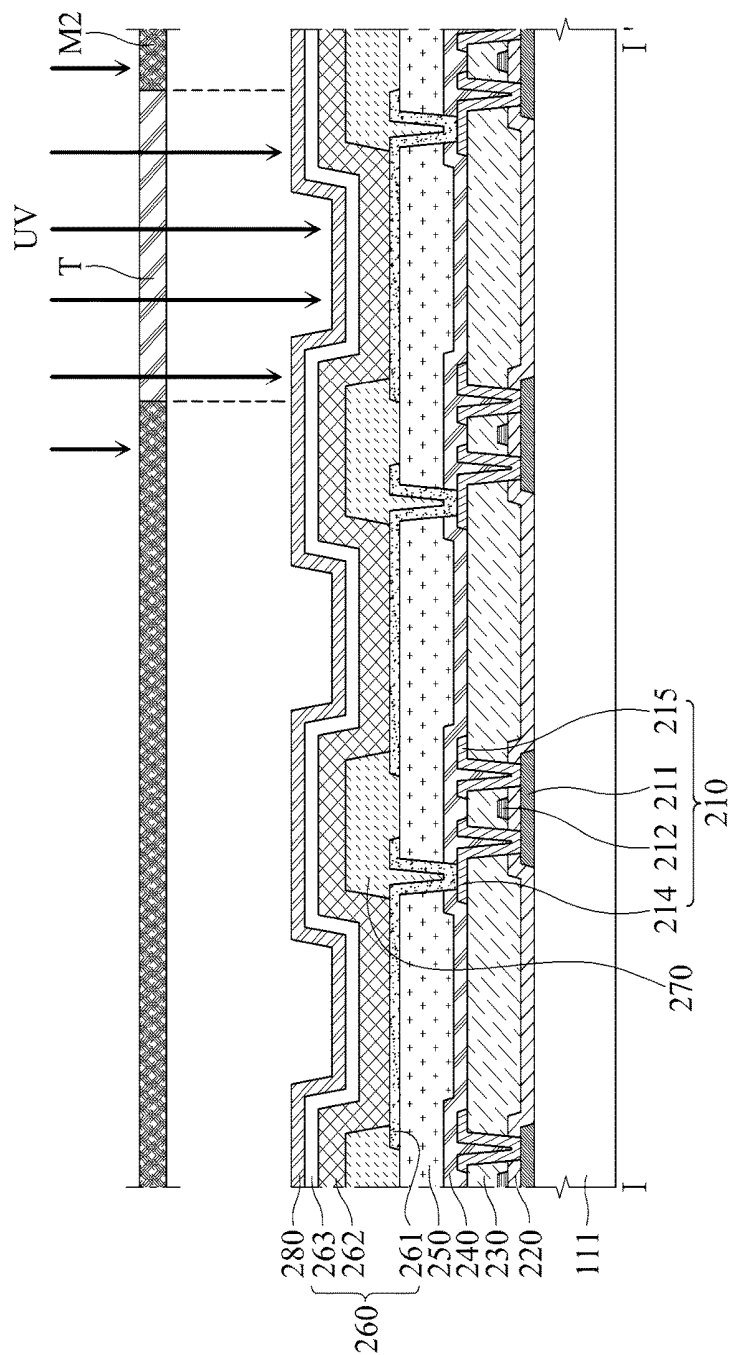


FIG. 9C

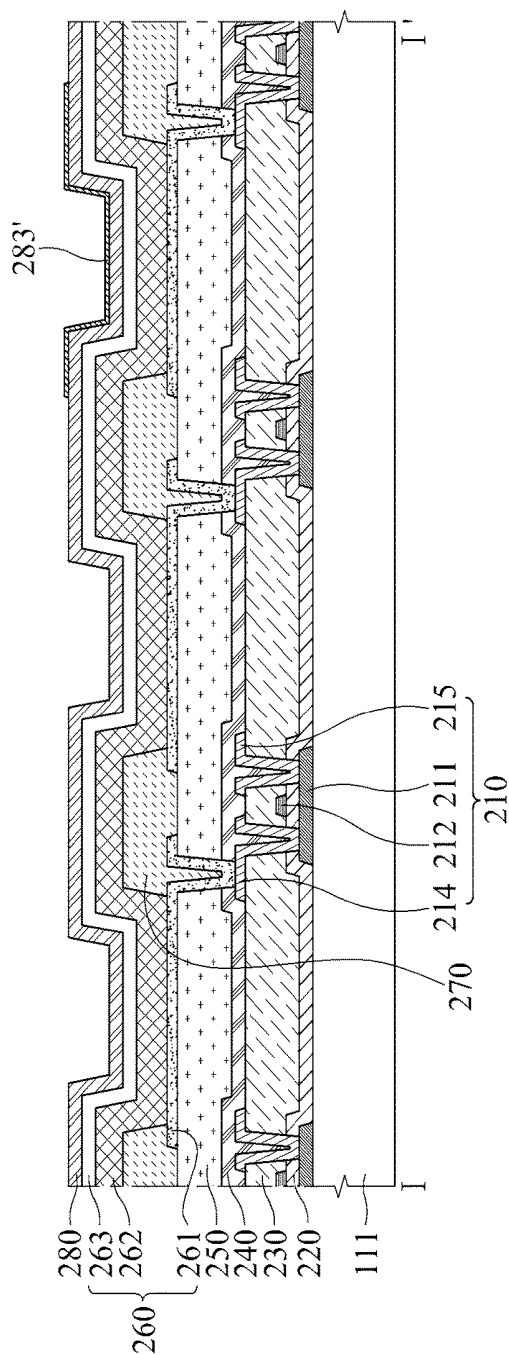


FIG. 9E

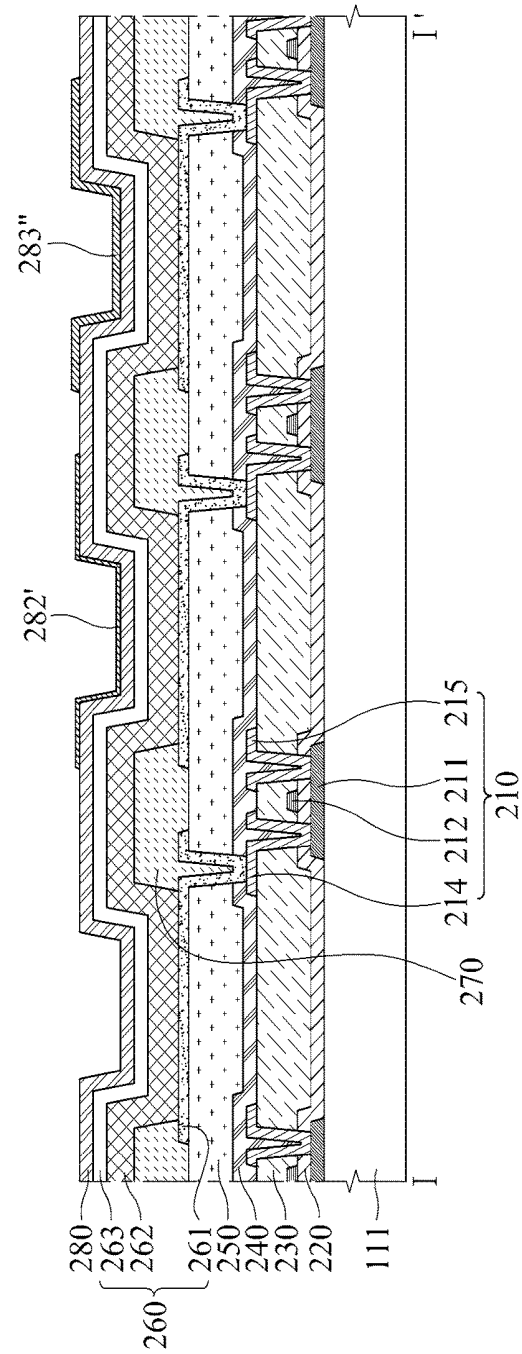


FIG. 9F

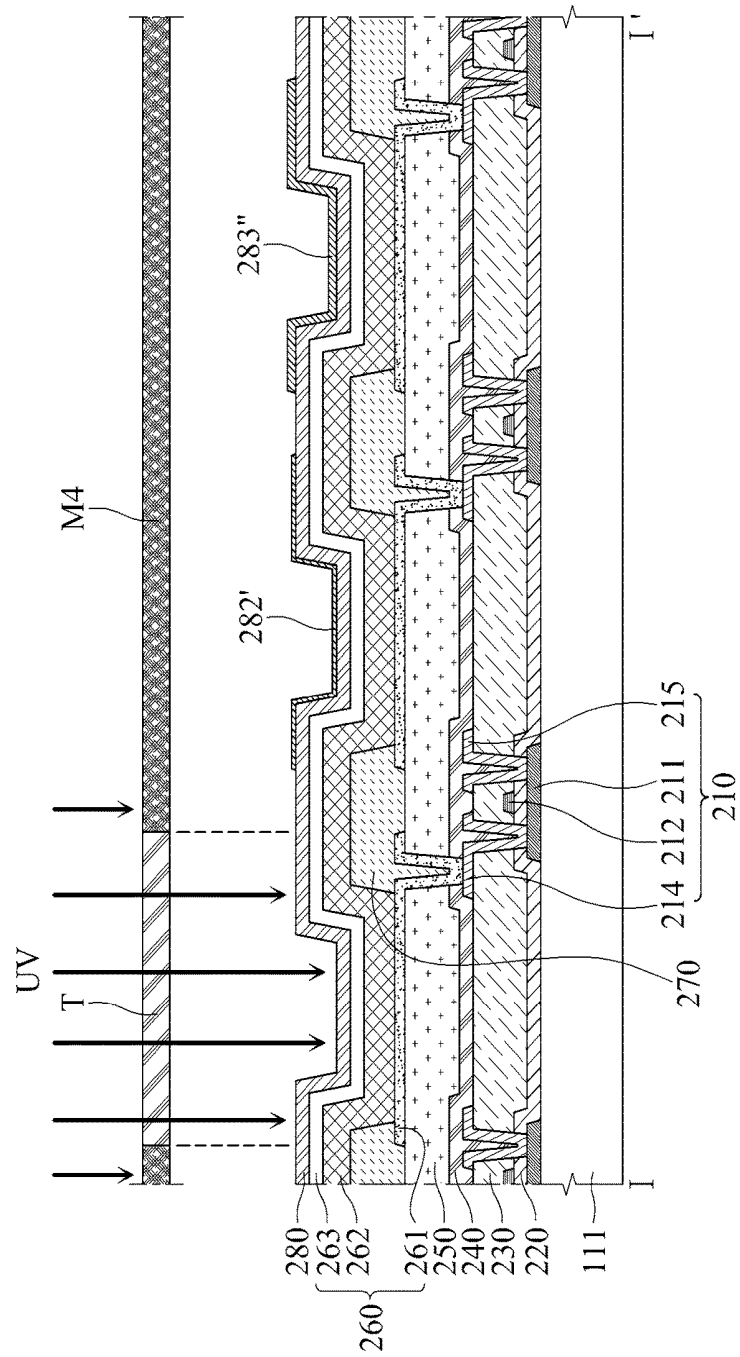


FIG. 9G

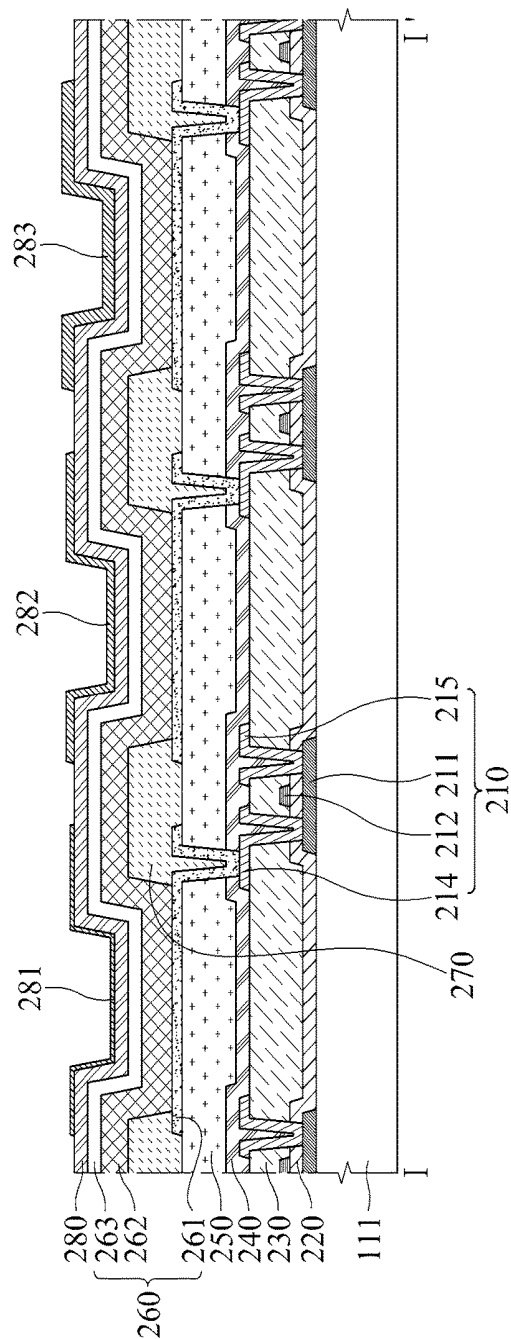


FIG. 9H

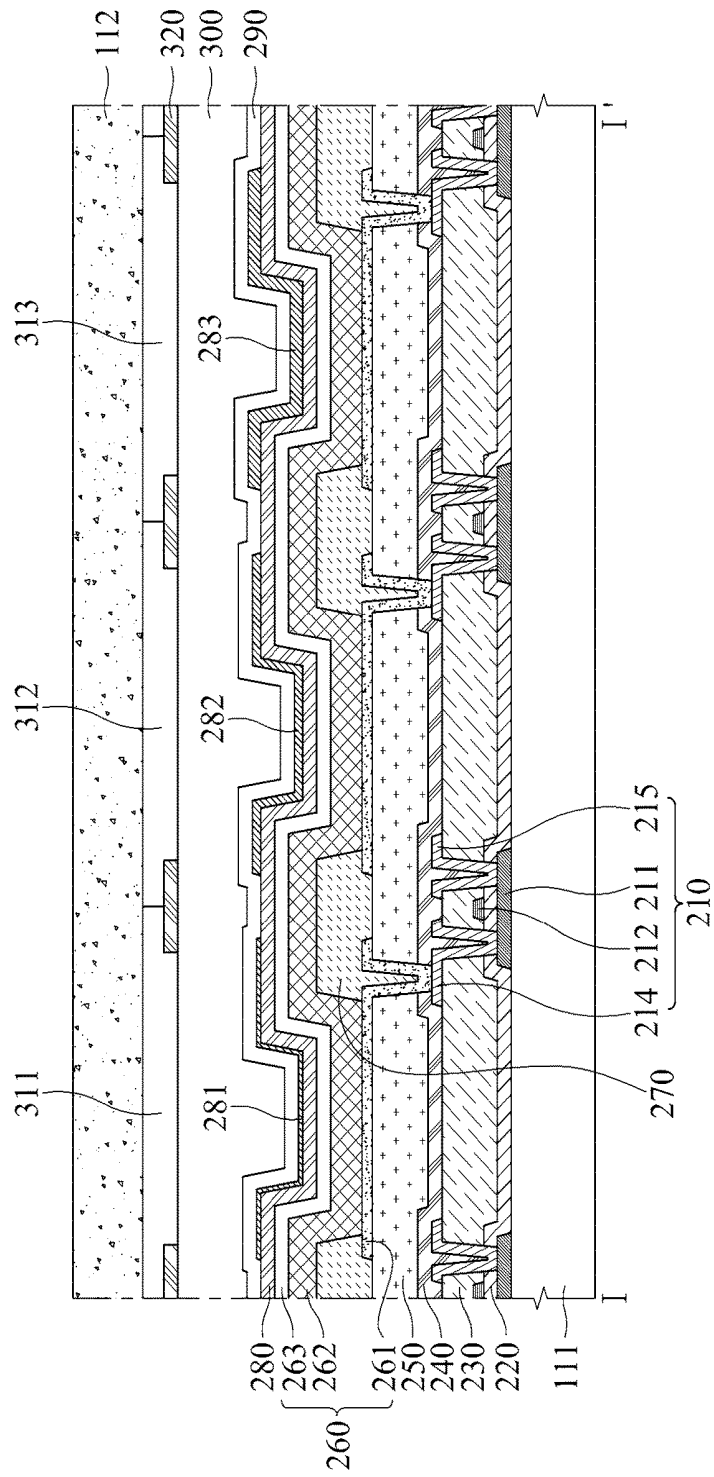


FIG. 10

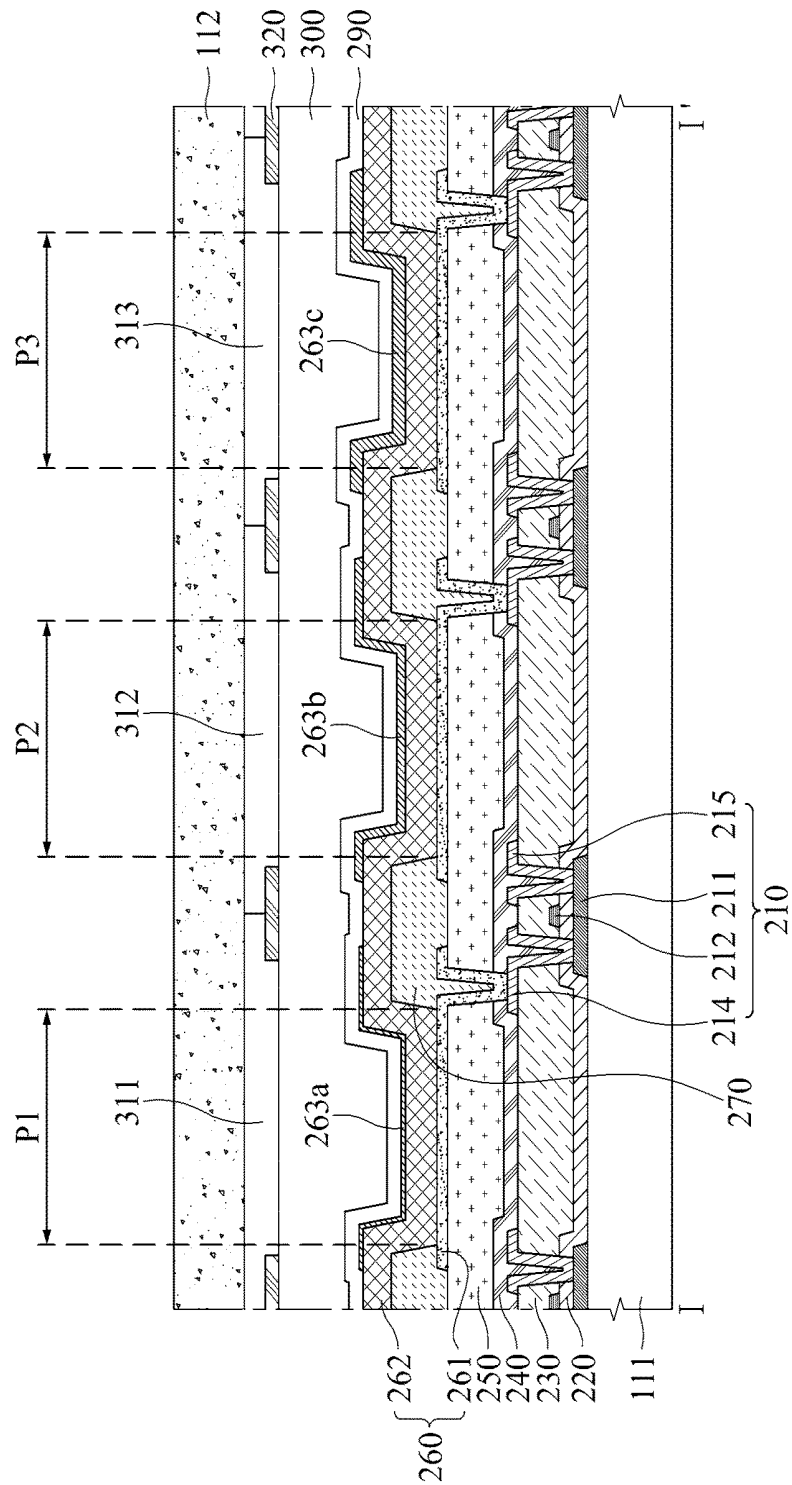


FIG. 11

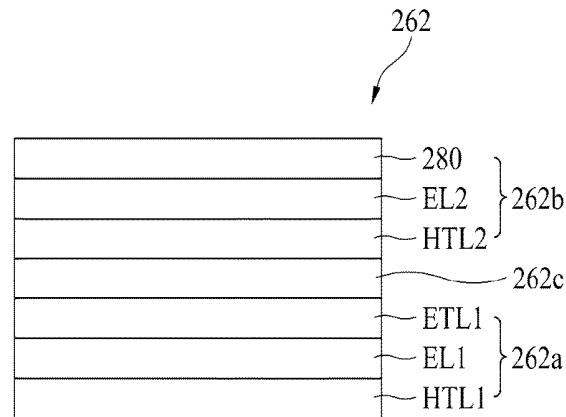


FIG. 12

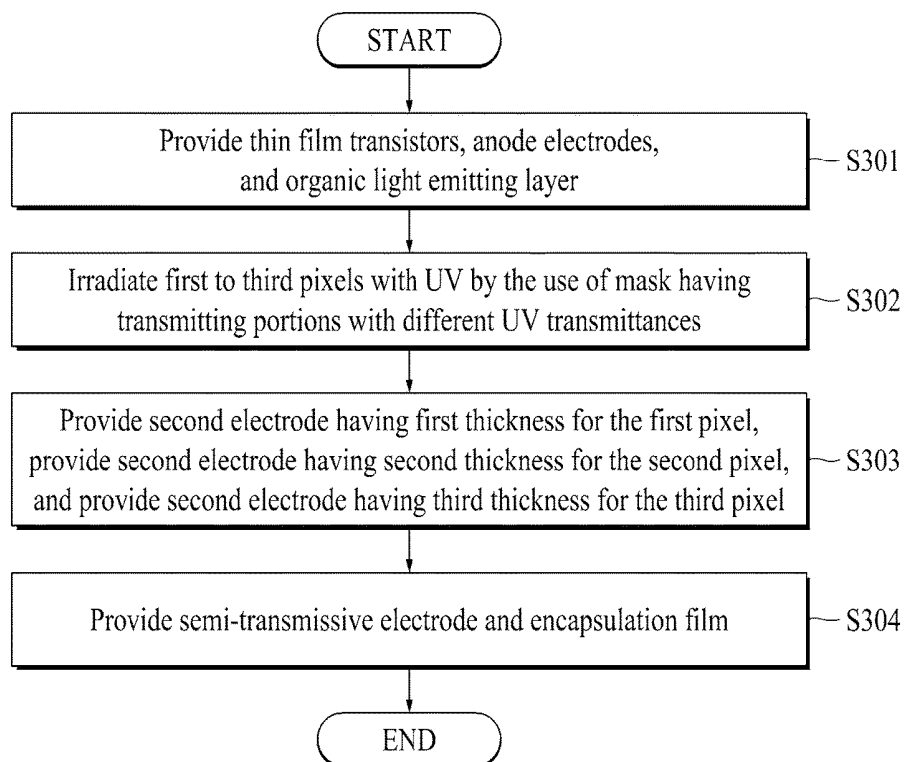


FIG. 13A

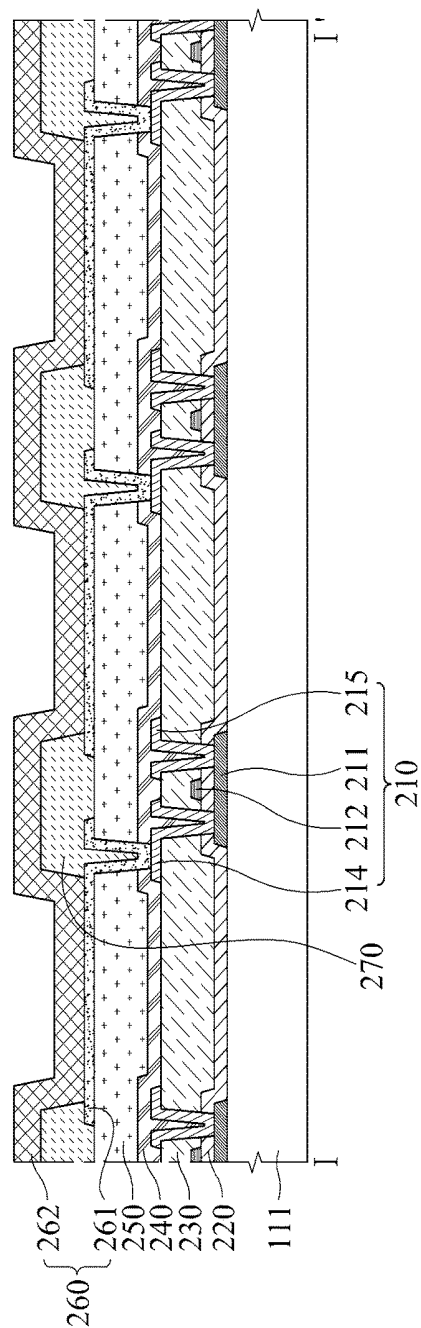


FIG. 13B

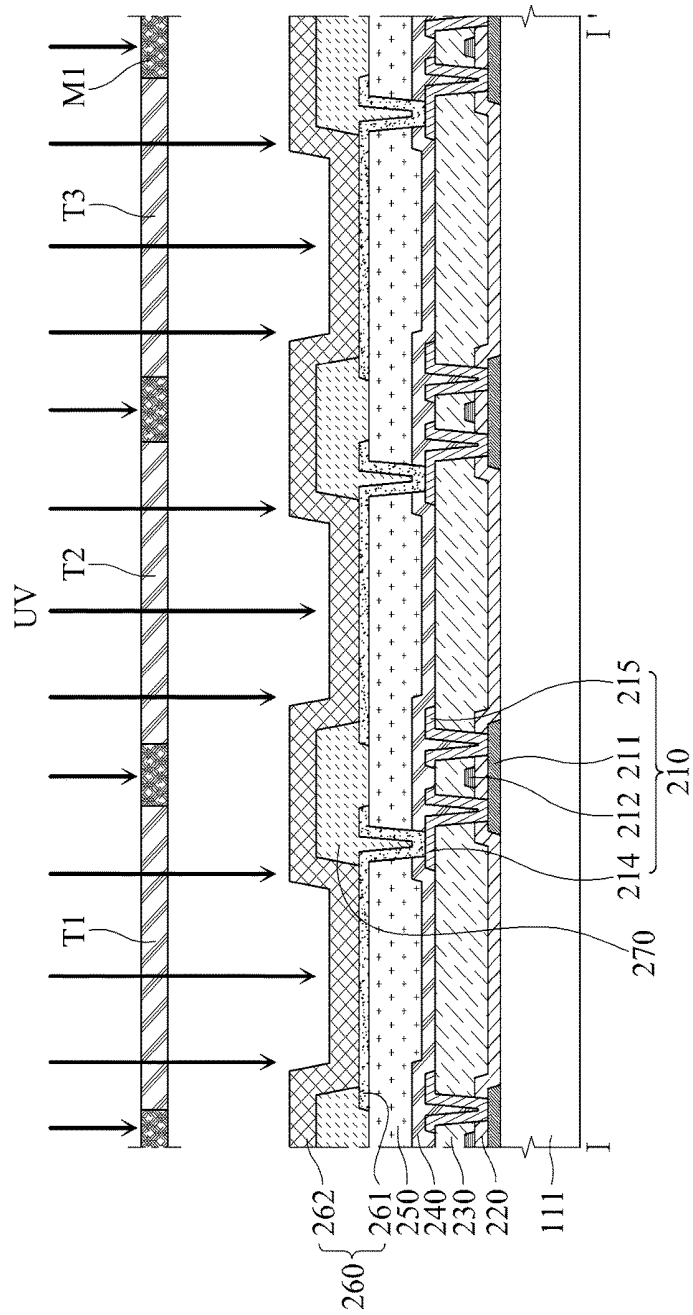


FIG. 13C

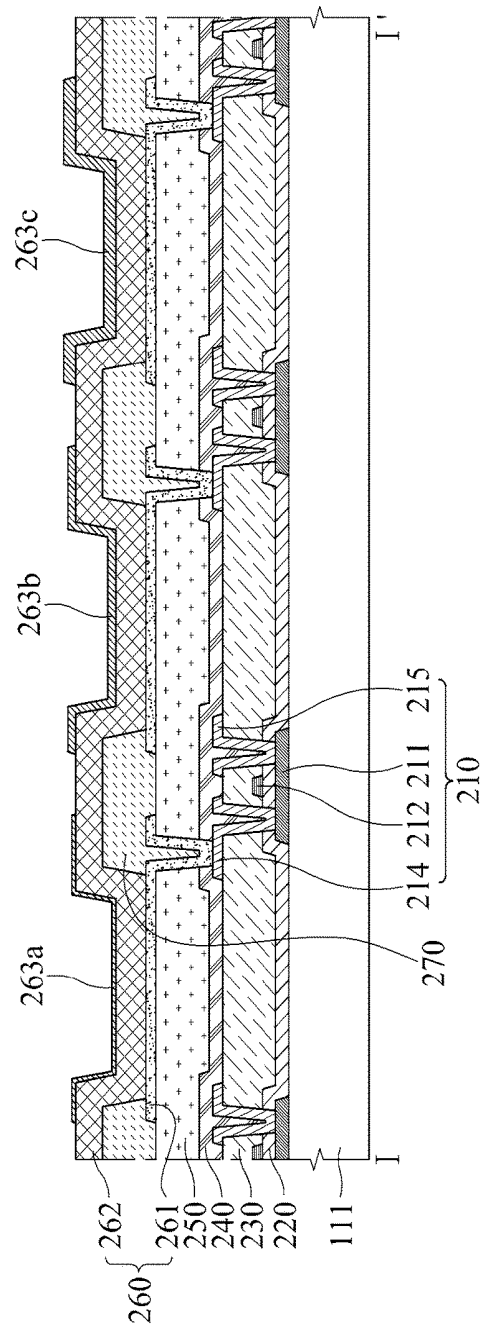


FIG. 13D

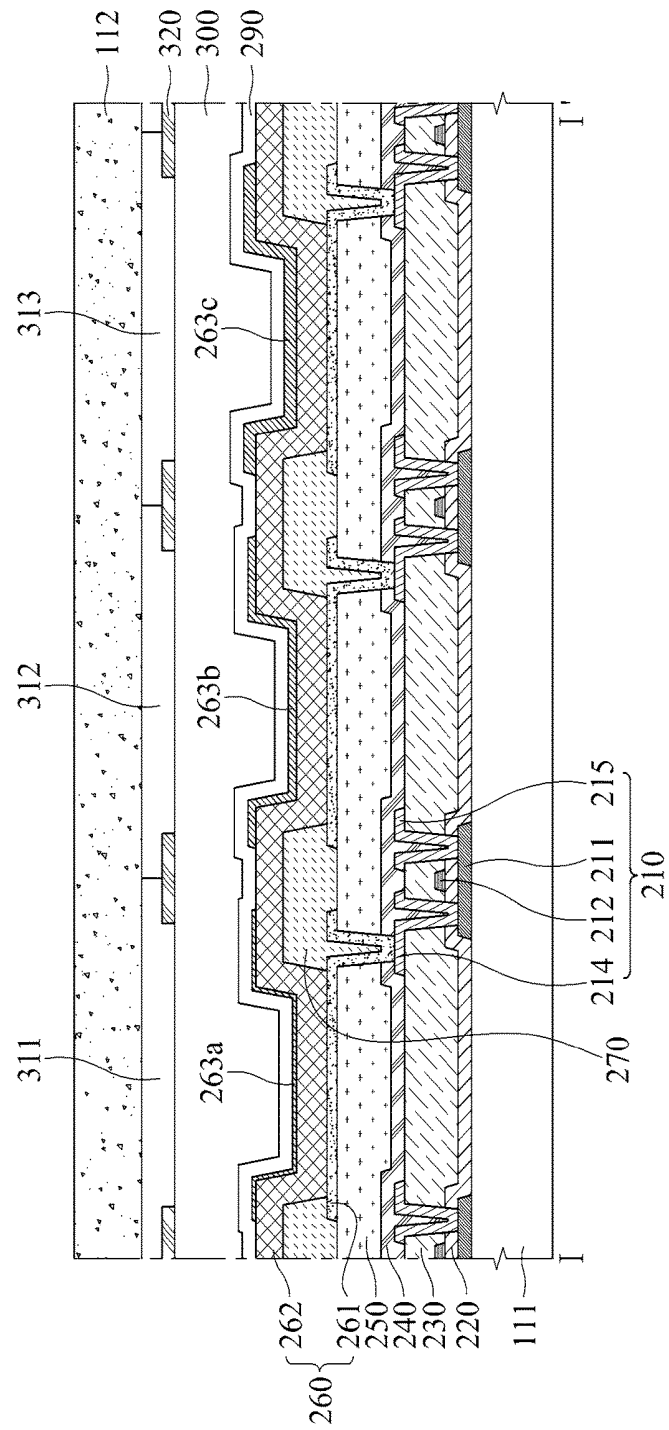


FIG. 14

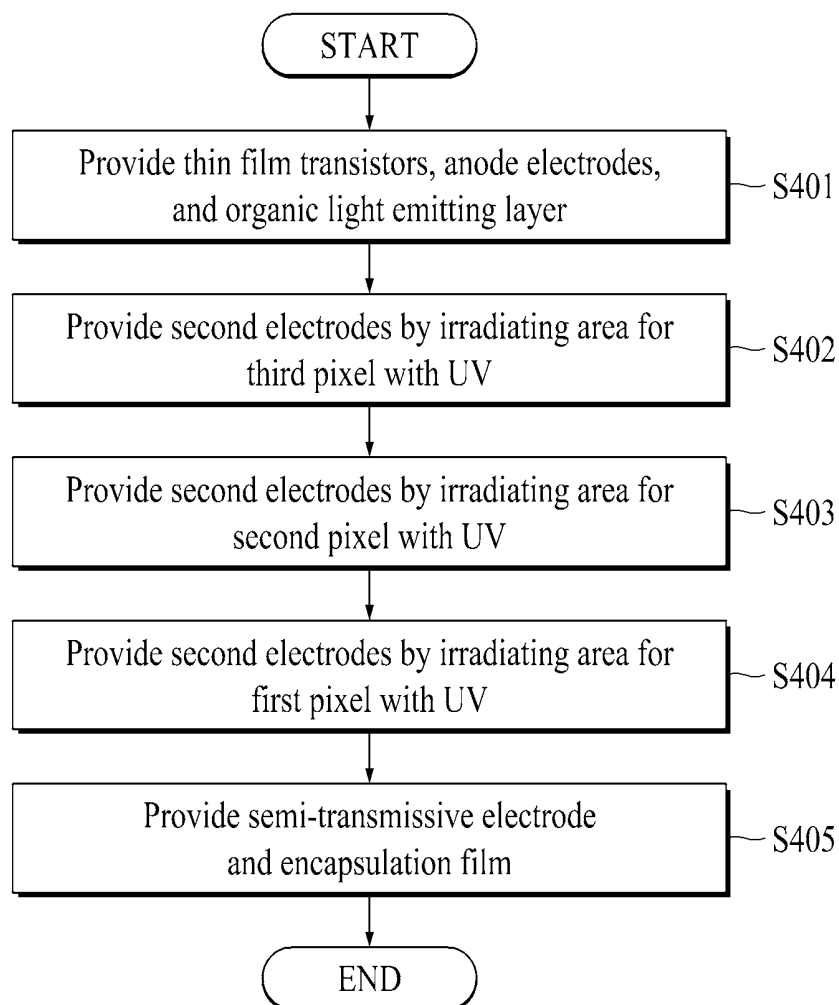


FIG. 15A

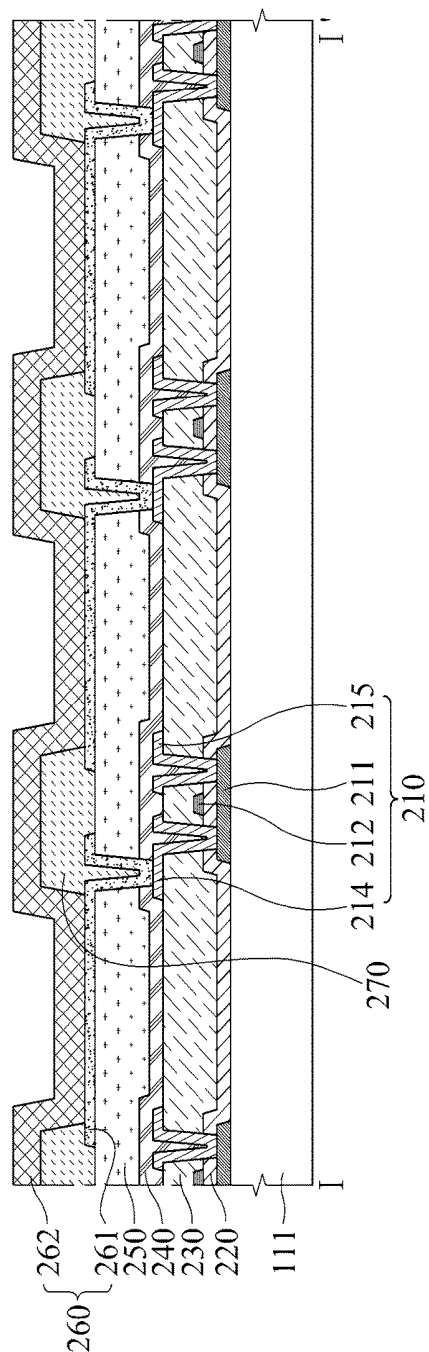


FIG. 15B

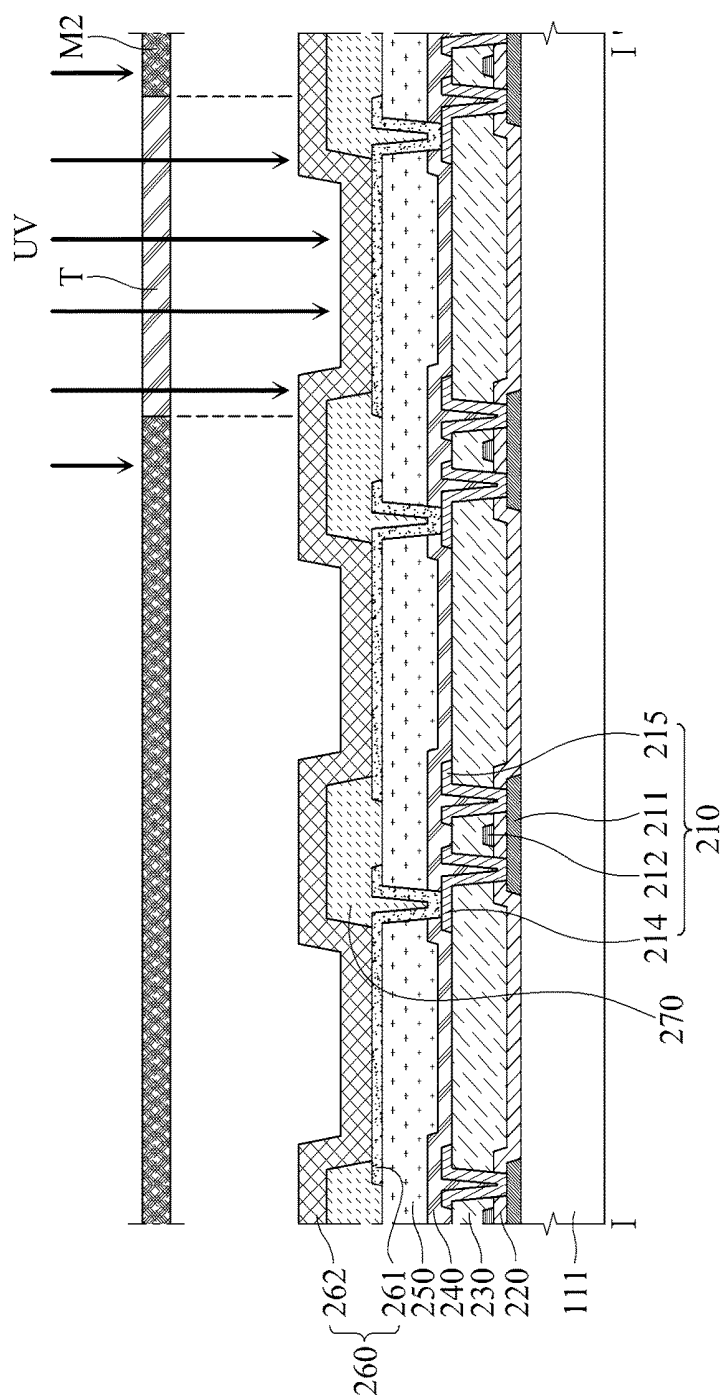


FIG. 15C

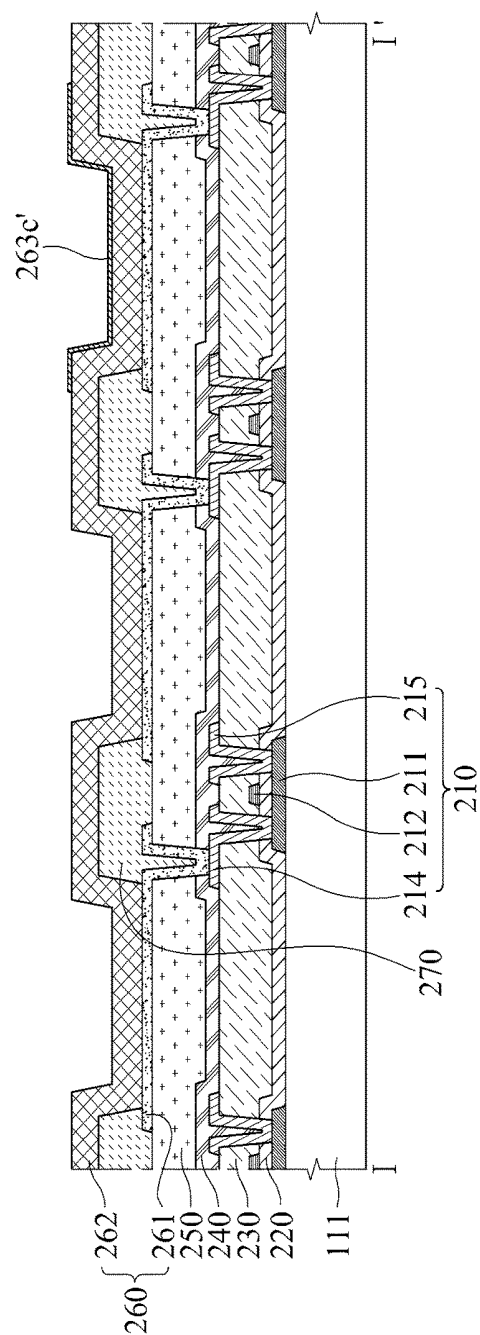


FIG. 15D

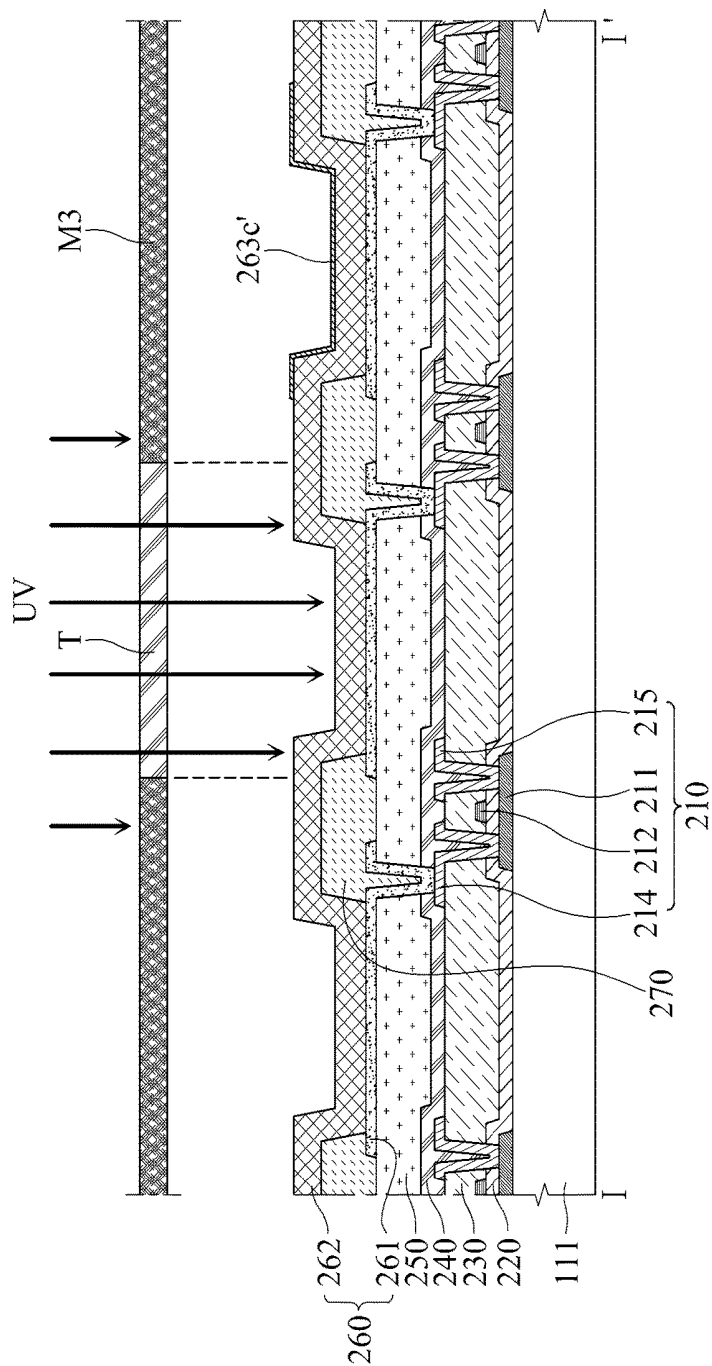


FIG. 15E

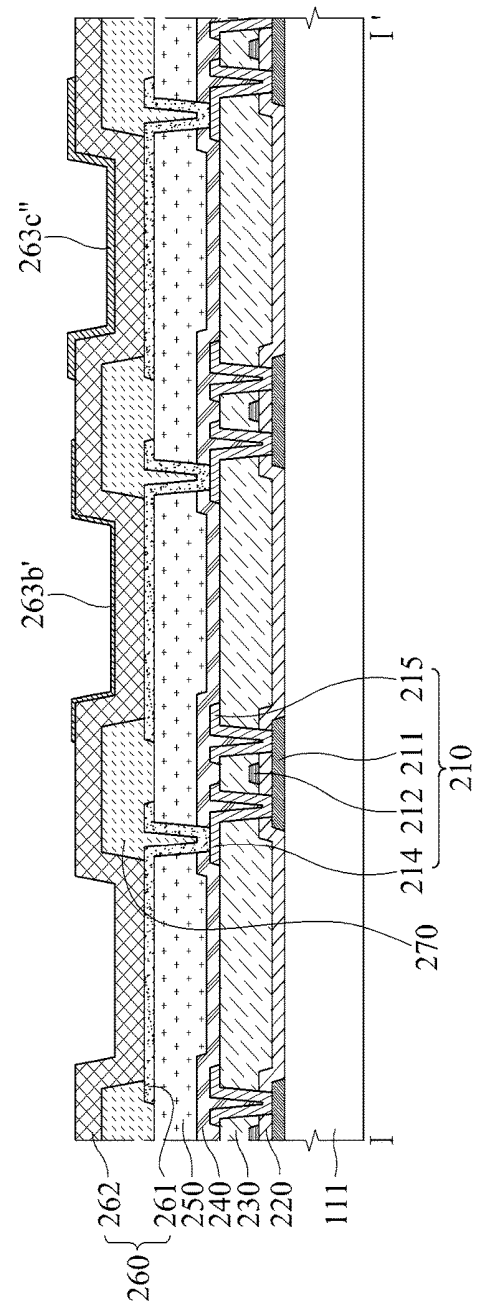


FIG. 15F

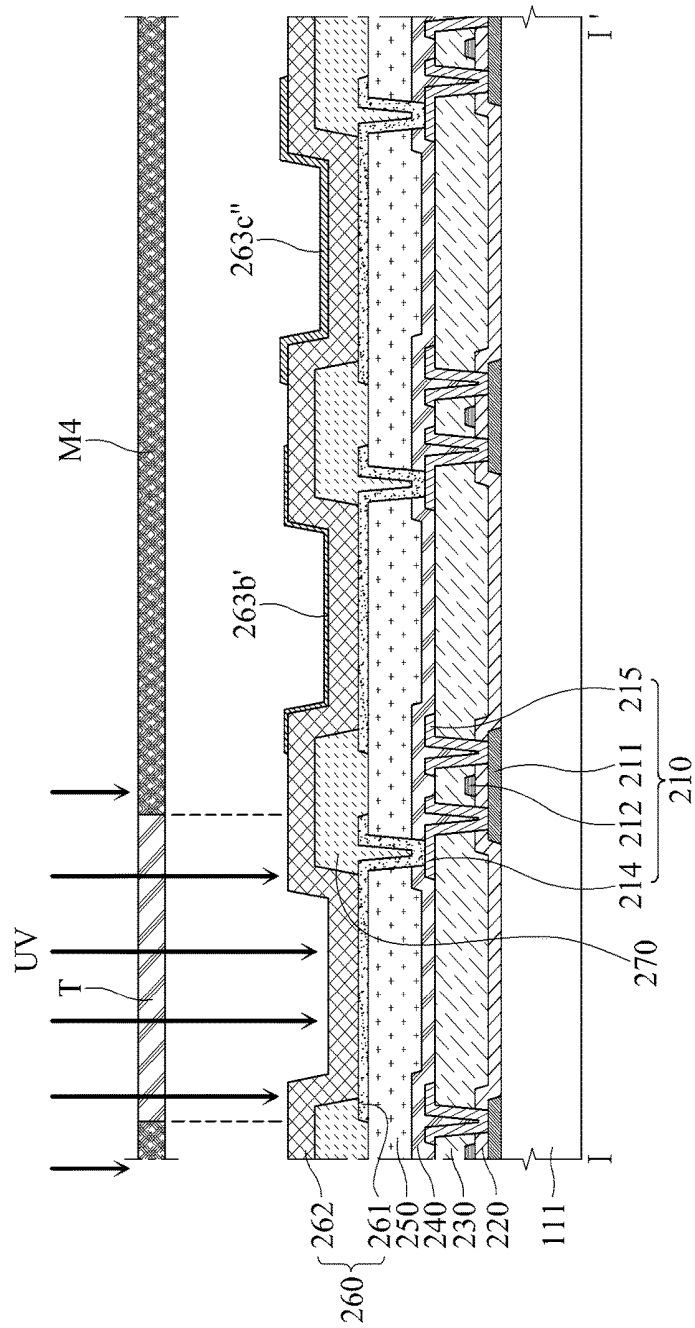


FIG. 15G

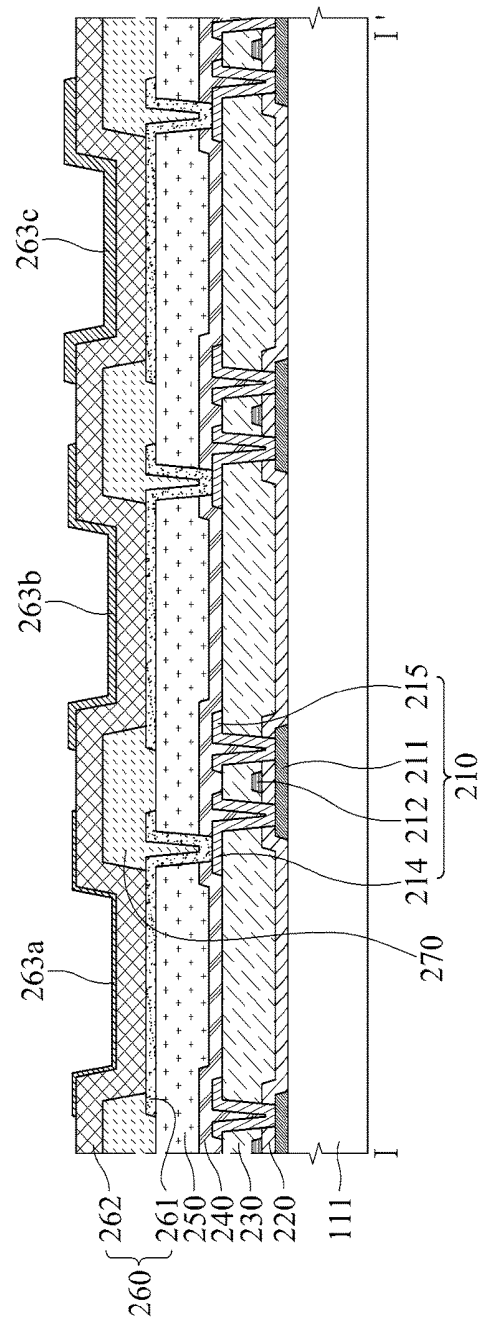
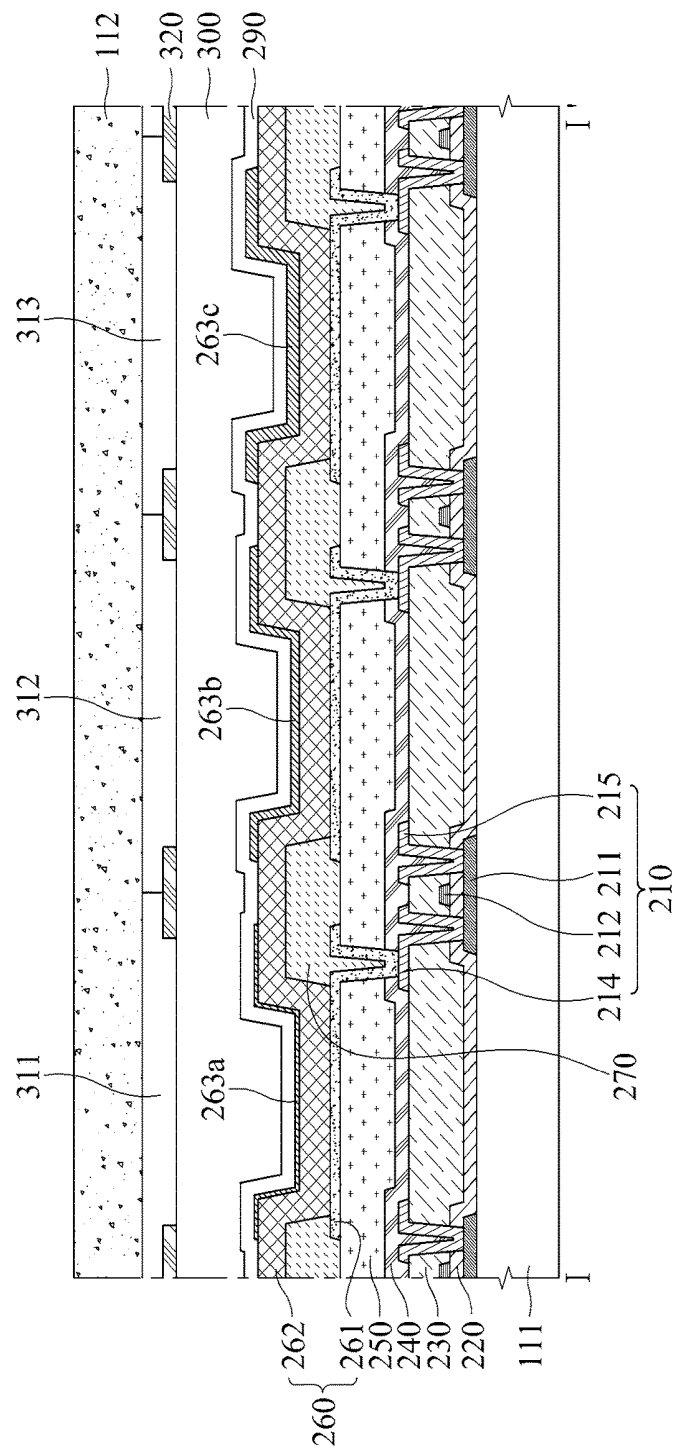


FIG. 15H



ORGANIC LIGHT EMITTING DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME

CROSS REFERENCE TO RELATED APPLICATIONS

This application claims priority to Republic of Korea Patent Application No. 10-2016-0160957 filed on Nov. 30, 2016, which is hereby incorporated by reference as if fully set forth herein.

BACKGROUND

Field of the Disclosure

Embodiments of the present disclosure relate to an organic light emitting display device and a method for manufacturing the same.

Discussion of the Related Art

With the advancement of an information-oriented society, various requirements for the display device of displaying an image are increasing. Thus, various display devices of a liquid crystal display (LCD) devices, a plasma display panel (PDP) devices, and an organic light emitting display (OLED) device have been utilized.

The OLED device is a self-light emitting display device. In comparison to the LCD device, the OLED device has wider viewing angle and greater contrast ratio. Also, the OLED device may be fabricated at a lightweight and slim size as it does not need a separate light source unlike the LCD device, and furthermore the OLED device is favorable in view of power consumption. In addition, the OLED device may be driven by a low D.C. voltage, and a response speed of the OLED device is fast. Especially, the OLED device may have the advantage of low manufacturing cost.

The OLED device may include pixels respectively provided with organic light emitting devices, and a bank for dividing the pixels so as to define the pixels. The bank functions as a pixel defining film. The organic light emitting device may include an anode electrode, a hole transporting layer, an organic light emitting layer, an electron transporting layer, and a cathode electrode. In this case, when a high potential voltage is applied to the anode electrode, and a low potential voltage is applied to the cathode electrode, holes and electrons are respectively moved to the organic light emitting layer via the hole transporting layer and the electron transporting layer, and are then combined to each other in the organic light emitting layer, to thereby emit light.

If the organic light emitting device includes only a white organic light emitting layer, the organic light emitting layer is formed as a common layer for the pixels. Accordingly, it is necessary to provide red, green, and blue color filters for realizing red, green, and blue colors, and a black matrix.

In case of the OLED device, the organic light emitting layer is deteriorated in accordance with a driving time, whereby a lifespan of the organic light emitting layer is short. Also, a polarizing plate for preventing a reflection of external light is attached to the OLED device, whereby some of light emitted from the organic light emitting layer may be lost by the polarizing plate. Accordingly, there is a need to provide a method for improving an emission efficiency of light emitted from the organic light emitting layer. In order to improve the emission efficiency, a micro-cavity structure may be applied to the organic light emitting device.

Herein, the micro-cavity indicates that the light-emission efficiency is improved by amplification and constructive interference of the light through repetitive reflection and re-reflection of the light emitted from the organic light emitting layer between the anode and cathode electrodes. In a top emission type wherein light advances to a direction of the cathode electrode, the anode electrode is formed of a reflection electrode, and the cathode electrode is formed of a semi-transmissive electrode, it is possible to improve the emission efficiency of light emitted from the organic light emitting layer by the use of micro-cavity structure.

Meanwhile, a wavelength of light in a red pixel emitted through the red color filter, a wavelength of light in a green pixel emitted through the green color filter, and a wavelength of light in a blue pixel emitted through the blue color filter are different from one another. Accordingly, in order to optimize the micro-cavity, a thickness of the anode electrode in the red pixel, a thickness of the anode electrode in the green pixel, and a thickness of the anode electrode in the blue pixel are different from each other so that it is possible to optimize a micro-cavity distance in each of the red, green, and blue pixels. However, a deposition process, a photo process, and an etching process have to be repetitively carried out for each of the red, green, and blue pixels so as to provide the anode electrodes having the different thicknesses in the respective red, green, and blue pixels. That is, if applying the micro-cavity structure, nine manufacturing processes are additionally carried out. Accordingly, if applying the micro-cavity structure, a manufacturing process is complicated, and a manufacturing cost is also increased.

SUMMARY

Accordingly, embodiments of the present disclosure are directed to an organic light emitting display device that substantially obviates one or more problems due to limitations and disadvantages of the related art, and a method for manufacturing the same.

An aspect of embodiments of the present disclosure is directed to provide an organic light emitting display device which is capable of reducing the number of manufacturing processes to apply a micro-cavity structure, and a method for manufacturing the same.

Additional advantages and features of embodiments of the disclosure will be set forth in part in the description which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of embodiments of the disclosure. The objectives and other advantages of embodiments of the disclosure may be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

To achieve these and other advantages and in accordance with the purpose of embodiments of the disclosure, as embodied and broadly described herein, there is provided an organic light emitting display (OLED) device that may include a pixel having a first subpixel, a second subpixel, and a third subpixel, wherein each of the first subpixel, the second subpixel, and the third subpixel includes a first electrode including a reflective metal material, an organic light emitting layer disposed on the first electrode, a second electrode disposed on the organic light emitting layer and formed of a transparent metal material, and a semi-transmissive electrode disposed on the second electrode, wherein a first distance between the first electrode and the semi-transmissive electrode in the first subpixel, a second distance between the first electrode and the semi-transmissive elec-

3

trode in the second subpixel, and a third distance between the first electrode and the semi-transmissive electrode in the third subpixel are different from one another.

In another aspect of an embodiment of the present disclosure, there is provided a method for manufacturing an OLED device that may include forming first electrodes on a first substrate, forming an organic light emitting layer on the first electrodes, forming a second electrode on the organic light emitting layer, and forming a photo-reactive organic film on the second electrode. The method further includes disposing a mask including a first transmitting portion, a second transmitting portion, and a third transmitting portion on the photo-reactive organic film, and irradiating UV onto the mask, wherein the first transmitting portion having a first UV transmittance is positioned above an area for a first subpixel, the second transmitting portion having a second UV transmittance, which is higher than the first UV transmittance, is positioned above an area for a second subpixel, and the third transmitting portion having a third UV transmittance, which is higher than the second UV transmittance, is positioned above an area for a third subpixel. The method further includes depositing a metal film on the photo-reactive organic film by the use of open mask, forming a first optical auxiliary layer having a first thickness in the first subpixel, forming a second optical auxiliary layer having a second thickness in the second subpixel, and forming a third optical auxiliary layer having a third thickness in the third subpixel. The open mask may have a fourth transmittance portion corresponding to a display area of the first substrate. The method further includes forming a semi-transmissive electrode on the first to third optical auxiliary layers.

In another aspect of an embodiment of the present disclosure, there is provided a method for manufacturing an OLED device that may include forming first electrodes on a first substrate, forming an organic light emitting layer on the first electrodes, forming a second electrode on the organic light emitting layer, and forming a photo-reactive organic film on the second electrode. The method further includes disposing a first mask having a first transmitting portion above an area for a first subpixel on the photo-reactive organic film, irradiating UV onto the area for the first subpixel, and depositing a first metal film with an open mask having a second transmitting portion corresponding to a display area of the first substrate. The method further includes disposing a second mask having a third transmitting portion above an area for a second subpixel on the photo-reactive organic film, irradiating UV onto the area for the second subpixel, and depositing a second metal film by the use of open mask. The method further includes forming a first optical auxiliary layer having a first thickness in the area for the first subpixel, a second optical auxiliary layer having a second thickness in the area for the second subpixel, and a third optical auxiliary layer having a third thickness in the area for the third subpixel by disposing a third mask having a fourth transmitting portion above an area for a third subpixel on the photo-reactive organic film, irradiating UV thereonto, and depositing a metal film by the use of open mask. The method further includes forming a semi-transmissive electrode on the first to third optical auxiliary layers.

Embodiments also relate to a light emitting display device. The light emitting display device includes a substrate, a first subpixel on the substrate, and a second subpixel on the substrate. The first subpixel includes a first bottom electrode, at least a first part of an organic light emitting layer on the first bottom electrode, a first conductive film on the first part of the organic light emitting layer, and at least a first part of a semi-transmissive electrode on the first

4

conductive film. The second subpixel includes a second bottom electrode, at least a second part of the organic light emitting layer on the second bottom electrode, a second conductive film on the second part of the organic light emitting layer, and at least a second part of the semi-transmissive electrode on the second conductive film. The thickness of the second conductive film is greater than a thickness of the first conductive film.

It is to be understood that both the foregoing general description and the following detailed description of embodiments of the present invention are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are included to provide a further understanding of embodiments of the invention and are incorporated in and constitute a part of this application, illustrate embodiment(s) of the invention and together with the description serve to explain the principle of embodiments of the invention. In the drawings:

FIG. 1 is a perspective view illustrating an OLED device according to one embodiment of the present disclosure;

FIG. 2 is a plane view illustrating a first substrate, a gate driver, a source drive IC, a flexible film, a circuit board, and a timing controller of FIG. 1 according to one embodiment of the present disclosure;

FIG. 3 is a plane view illustrating one example of subpixels in a display area;

FIG. 4 is a cross sectional view along I-I' of FIG. 3 according to one embodiment of the present disclosure;

FIG. 5 is a chemical formula showing one example of a photo-reactive organic film;

FIG. 6 is a flow chart illustrating a method for manufacturing an OLED device according to one embodiment of the present disclosure;

FIGS. 7A to 7D are cross sectional views illustrating the method for manufacturing the OLED device according to one embodiment of the present disclosure;

FIG. 8 is a flow chart illustrating a method for manufacturing an OLED device according to another embodiment of the present disclosure;

FIGS. 9A to 9H are cross sectional views illustrating the method for manufacturing the OLED device according to another embodiment of the present disclosure;

FIG. 10 is a cross sectional view showing another example along I-I' of FIG. 3 according to another embodiment of the present disclosure;

FIG. 11 illustrates one example of an organic light emitting layer of FIG. 10;

FIG. 12 is a flow chart illustrating a method for manufacturing an OLED device according to another embodiment of the present disclosure;

FIGS. 13A to 13D are cross sectional views illustrating the method for manufacturing the OLED device according to another embodiment of the present disclosure;

FIG. 14 is a flow chart illustrating a method for manufacturing an OLED device according to another embodiment of the present disclosure; and

FIGS. 15A to 15H are cross sectional views illustrating the method for manufacturing the OLED device according to another embodiment of the present disclosure.

DETAILED DESCRIPTION OF THE INVENTION

Reference will now be made in detail to the exemplary embodiments of the present invention, examples of which

are illustrated in the accompanying drawings. Wherever possible, the same reference numbers will be used throughout the drawings to refer to the same or like parts.

Advantages and features of the present invention, and implementation methods thereof will be clarified through following embodiments described with reference to the accompanying drawings. The present invention may, however, be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the present invention to those skilled in the art. Further, the present invention is only defined by scopes of claims.

A shape, a size, a ratio, an angle, and a number disclosed in the drawings for describing embodiments of the present invention are merely an example, and thus, the present invention is not limited to the illustrated details. Like reference numerals refer to like elements throughout. In the following description, when the detailed description of the relevant known function or configuration is determined to unnecessarily obscure the important point of the present invention, the detailed description will be omitted.

In a case where 'comprise', 'have', and 'include' described in the present specification are used, another part may be added unless 'only~' is used. The terms of a singular form may include plural forms unless referred to the contrary.

In construing an element, the element is construed as including an error region although there is no explicit description.

In describing a position relationship, for example, when the positional order is described as 'on~', 'above~', 'below~', and 'next~', a case which is not contact may be included unless 'just' or 'direct' is used.

In describing a time relationship, for example, when the temporal order is described as 'after~', 'subsequent~', 'next~', and 'before~', a case which is not continuous may be included unless 'just' or 'direct' is used.

It will be understood that, although the terms "first", "second", etc. may be used herein to describe various elements, these elements should not be limited by these terms. These terms are only used to distinguish one element from another. For example, a first element could be termed a second element, and, similarly, a second element could be termed a first element, without departing from the scope of the present invention.

Also, "X-axis direction", "Y-axis direction", and "Z-axis direction" are not limited to a perpendicular geometric configuration. That is, "X-axis direction", "Y-axis direction", and "Z-axis direction" may include an applicable wide range of a functional configuration.

Also, it should be understood that the term "at least one" includes all combinations related with any one item. For example, "at least one among a first element, a second element and a third element" may include all combinations of two or more elements selected from the first, second and third elements as well as each element of the first, second and third elements. Also, if it is mentioned that a first element is positioned "on or above" a second element, it should be understood that the first and second elements may be brought into contact with each other, or a third element may be interposed between the first and second elements.

Features of various embodiments of the present invention may be partially or overall coupled to or combined with each other, and may be variously inter-operated with each other and driven technically as those skilled in the art can suffi-

ciently understand. The embodiments of the present invention may be carried out independently from each other, or may be carried out together in co-dependent relationship.

Hereinafter, an organic light emitting display (OLED) device according to the embodiment of the present disclosure and a method for manufacturing the same will be described in detail with reference to the accompanying drawings.

FIG. 1 is a perspective view illustrating an OLED device according to one embodiment of the present disclosure. FIG. 2 is a plane view illustrating a first substrate, a gate driver, a source drive IC, a flexible film, a circuit board, and a timing controller of FIG. 1 according to an embodiment of the present disclosure.

Referring to FIGS. 1 and 2, a display device 100 according to one embodiment of the present disclosure may include a display panel 110, a gate driver 120, a source drive integrated circuit (source drive IC) 130, a flexible film 140, a circuit board 150, and a timing controller 160.

The display panel 110 may include a first substrate 111 and a second substrate 112. The second substrate 112 may be an encapsulation substrate. The first substrate 111 may be a plastic film or a glass substrate. The second substrate 112 may be a plastic film, a glass substrate, or an encapsulation film (or protection film).

On one surface of the first substrate 111 facing the second substrate 112, there are gate lines, data lines, and subpixels. The subpixels are prepared in respective areas defined by crossing the gate lines and the data lines.

Each of the subpixels may include a thin film transistor, and an organic light emitting device including a first electrode, an organic light emitting layer, and a second electrode. If a gate signal is supplied from a gate line to each subpixel through the thin film transistor, a predetermined current is supplied to the organic light emitting device in accordance with a data voltage of the data line. Accordingly, the organic light emitting device for each of the subpixels may emit light with a predetermined brightness in accordance with the predetermined current. A structure of each of the subpixels will be described in detail with reference to FIG. 4.

As shown in FIG. 2, the display panel 110 may include a display area (DA) provided with the subpixels for displaying an image, and a non-display area (NDA) in which an image is not displayed. The gate lines, the data lines, and the subpixels may be provided in the display area (DA), and the gate driver 120 and pads may be provided in the non-display area (NDA).

The gate driver 120 supplies gate signals to the gate lines in accordance with a gate control signal which is provided from the timing controller 160. The gate driver 120 may be provided in one side of the display area (DA) of the display panel 110, or the non-display area (NDA) of both peripheral sides of the display panel 110 by a gate driver in panel (GIP) method. In another way, the gate driver 120 may be manufactured in a driving chip, may be mounted on the flexible film, and may be attached to one side of the display area (DA) of the display panel 110, or the non-display area (NDA) of both peripheral sides of the display panel 110 by a tape automated bonding (TAB) method.

The source drive IC 130 receives digital video data and source control signals from the timing controller 160. The source drive IC 130 converts the digital video data into analog data voltages in accordance with the source control signal, and supplies the analog data voltages to the data lines. If the source drive IC 130 is manufactured in a driving

chip, the source drive IC **130** may be mounted on the flexible film **140** by a chip on film (COF) method or a chip on plastic (COP) method.

The pads such as data pads may be provided in the non-display area (NDA) of the display panel **110**. In the flexible film **140**, there are lines for connecting the pads with the source drive IC **130**, and lines for connecting the pads with the lines of the circuit board **150**. The flexible film **140** is attached to the pads by the use of anisotropic conducting film, whereby the pads may be connected with the lines of the flexible film **140**.

The circuit board **150** may be attached to the flexible film **140**. A plurality of circuits, which are realized in a plurality of driving chips, may be mounted on the circuit board **150**. For example, the timing controller **160** may be mounted on the circuit board **150**. The circuit board **150** may be a printed circuit board or a flexible printed circuit board.

The timing controller **160** receives digital video data and a timing signal from an external system board via a cable of the circuit board **150**. The timing controller **160** generates the gate control signal for controlling an operation timing of the gate driver **120** and the source control signal for controlling the source drive IC **130** on the basis of the timing signal. The timing controller **160** supplies the gate control signal to the gate driver **120**, and supplies the source control signal to the source drive IC **130**.

FIG. 3 is a plane view illustrating one example of the subpixels in the display area. For convenience of explanation, FIG. 3 shows only a pixel including subpixels (P1, P2, P3), bank (BANK), and black matrix (BM).

Referring to FIG. 3, each of the subpixels (P1, P2, P3) is a light-emission area which is obtained by sequentially depositing a first electrode corresponding to an anode electrode, an organic light emitting layer, and a second electrode corresponding to a cathode electrode, wherein holes and electrons are respectively supplied from the first electrode and the second electrode, and are then combined with each other in the organic light emitting layer so as to emit light.

The organic light emitting layer of the subpixels (P1, P2, P3) may be provided in a common layer for the subpixels (P1, P2, P3), to thereby emit white light. In this case, a first color filter is disposed in the first subpixel (P1), a second color filter is disposed in the second subpixel (P2), and a third color filter is disposed in the third subpixel (P3). The first subpixel (P1) emits first-color light by the first color filter, the second subpixel (P2) emits second-color light by the second color filter, and the third subpixel (P3) emits third-color light by the third color filter.

The first to third subpixels (P1, P2, P3) may be defined as a pixel (PU). In this case, the first subpixel P1 may be a red pixel, the second subpixel P2 may be a green subpixel, and the third subpixel P3 may be a blue subpixel, but may not be limited to this structure. For example, red, green, blue, and white pixels may be defined as a pixel (PU).

The bank (BANK) is provided to divide the subpixels (P1, P2, P3), whereby the bank (BANK) serves as a pixel defining film for defining the subpixels (P1, P2, P3).

The black matrix (BM) is provided to divide the color filters. The black matrix (BM) may be overlapped with the bank (BANK) so as to prevent light of any one subpixel from being emitted toward the neighboring subpixel and mixed with light of the neighboring subpixel.

FIG. 4 is a cross sectional view illustrating one example along cross-section I-I' of FIG. 3.

Referring to FIG. 4, a buffer film is provided on one surface of the first substrate **111** facing the second substrate **112**. The buffer film is provided on one surface of the first

substrate **111** so as to protect thin film transistors **210** and organic light emitting devices **260** from moisture permeating through the first substrate **111** which is vulnerable to moisture permeability. The buffer film may be formed of a plurality of inorganic films deposited alternately. For example, the buffer film may be formed in a multi-layered structure by alternately depositing at least one inorganic film from a silicon oxide film (SiOx), a silicon nitride film (SiNx), and silicon oxynitride (SiON). It is possible to omit the buffer film.

The thin film transistor **210** is provided on the buffer film. The thin film transistor **210** includes an active layer **211**, a gate electrode **212**, a source electrode **213**, and a drain electrode **214**. In FIG. 4, the thin film transistor **210** is provided in a top gate type where the gate electrode **212** is positioned above the active layer **211**, but not limited to this type. For example, the thin film transistor **210** may be provided in a bottom gate type where the gate electrode **212** is positioned below the active layer **211**, or a double gate type where the gate electrode **212** is positioned both above and below the active layer **211**.

The active layer **211** is provided on the buffer film. The active layer **211** may be formed a silicon-based semiconductor material or an oxide-based semiconductor material. A light shielding layer may be additionally provided between the buffer film and the active layer **211** so as to block external light being incident on the active layer **211**.

A gate insulating film **220** may be provided on the active layer **211**. The gate insulating film **220** may be formed in a single-layered structure of the inorganic insulating material such as silicon oxide (SiOx) or silicon nitride (SiNx), or a multi-layered structure of the above silicon oxide (SiOx) and silicon nitride (SiNx).

The gate electrode **212** and gate line may be provided on the gate insulating film **220**. The gate electrode **212** and gate line may be formed in a single-layered structure or multi-layered structure among molybdenum (Mo), aluminum (Al), chrome (Cr), aurum (Au), titanium (Ti), nickel (Ni), neodymium (Nd), copper (Cu) and their alloys.

An insulating interlayer **230** may be provided on the gate electrode **212** and gate line. The insulating interlayer **230** may be formed in a single-layered structure of the inorganic insulating material such as silicon oxide (SiOx) or silicon nitride (SiNx), or a multi-layered structure of the above silicon oxide (SiOx), silicon nitride (SiNx) and their alloys.

The source electrode **214**, the drain electrode **215**, and the data line may be provided on the insulating interlayer **230**. Each of the source electrode **214** and the drain electrode **215** may be connected with the active layer **211** via a contact hole penetrating through the gate insulating film **220** and the insulating interlayer **230**. The source electrode **214**, the drain electrode **215**, and the data line may be formed in a single-layered structure or multi-layered structure among molybdenum (Mo), aluminum (Al), chrome (Cr), aurum (Au), titanium (Ti), nickel (Ni), neodymium (Nd), copper (Cu) and their alloys.

A protection film **240** for an insulation of the thin film transistor **210** may be provided on the source electrode **214**, the drain electrode **215**, and the data line. The protection film **240** may be formed in a single-layered structure of the inorganic material such as silicon oxide (SiOx) or silicon nitride (SiNx), or a multi-layered structure of the above silicon oxide (SiOx) and silicon nitride (SiNx).

A planarization film **250** may be provided on the protection film **240** so as to planarize a step difference area caused by the thin film transistor **210**. The planarization film **250**

may be formed of an organic material, for example, acryl resin, epoxy resin, phenolic resin, polyamide resin, polyimide resin, and etc.

The organic light emitting device **260** and the bank **270** are provided on the planarization film **250**. The organic light emitting device **260** may include the first electrode **261**, the organic light emitting layer **262**, and the second electrode **263**. The first electrode **261** may serve as an anode electrode, and the second electrode **263** may serve as a cathode electrode.

The first electrode **261** may be provided on the planarization film **250**. The first electrode **261** may also be referred to as a bottom electrode. The first electrode **261** may be connected with the source electrode **214** of the thin film transistor **210** via a contact hole penetrating through the protection film **240** and the planarization film **250**. According as the OLED device according to the embodiment of the present disclosure is formed in the top emission type, the first electrode **261** may include a reflection metal material for reflecting light from the organic light emitting layer **262** to the second electrode **263**. For example, the first electrode **261** may be formed of a metal material with high reflectance, and more particularly, a deposition structure of aluminum and titanium (Ti/Al/Ti), a deposition structure of aluminum and Indium Tin Oxide (ITO/Al/ITO), an APC alloy, and a deposition structure of APC alloy and Indium Tin Oxide (ITO/APC/ITO). Herein, the APC alloy is an alloy of argentums (Ag), palladium (Pd), and copper (Cu).

The bank **270** is provided to cover the edge of the first electrode **261** on the planarization film **250**, to thereby divide the subpixels (P1, P2, P3). That is, the bank **270** functions as the pixel defining film so as to define the subpixels (P1, P2, P3).

Each of the subpixels (P1, P2, P3) indicates a light-emission area, wherein the first electrode **261** corresponding to the anode electrode, the organic light emitting layer **262**, and the second electrode **263** corresponding to the cathode electrode are sequentially deposited in each subpixel, and hole and electron are respectively supplied from the first electrode **261** and the second electrode **263**, and are then combined with each other in the organic light emitting layer **262** so as to emit light. In this case, the area for the bank **270** does not emit light, whereby the area for the bank **270** may be defined as a non-emission area.

The bank **270** may be formed of an organic material, for example, acryl resin, epoxy resin, phenolic resin, polyamide resin, polyimide resin, and etc.

The organic light emitting layer **262** is provided on the first electrode **261** and the bank **270**. The organic light emitting layer **262** is a common layer provided on the subpixels (P1, P2, P3) in common. The organic light emitting layer may be a white light emitting layer for emitting white light. In this case, the organic light emitting layer **262** may have a tandem structure of 2 stacks or more than 2 stacks. Each stack may include a hole transporting layer, at least one light emitting layer, and an electron transporting layer. Each subpixel may include a corresponding part of the organic light emitting layer **262** disposed on the first electrode **261** of the subpixel. Thus, the first subpixel P1 may include at least a first part of the organic light emitting layer **262** on the first electrode **261** of the first subpixel P1, the second subpixel P2 may include at least a second part of the organic light emitting layer **262** on the first electrode **261** of the second subpixel P2, and the third subpixel P3 may include at least a third part of the organic light emitting layer **262** on the first electrode **261** of the third subpixel P3.

Between each of the stacks, there may be a charge generation layer. The charge generation layer may include an n-type charge generation layer positioned adjacent to the lower stack, and a p-type charge generation layer provided on the n-type charge generation layer and positioned adjacent to the upper stack. The n-type charge generation layer injects the electron into the lower stack, and the p-type charge generation layer injects the hole into the upper stack. The n-type charge generation layer may be formed of an organic layer obtained by doping an organic host material having an electron transporting capacity with alkali metal such as lithium (Li), natrium (Na), kalium (K) or cesium (Cs), or alkali earth metal such as magnesium (Mg), strontium (Sr), barium (Ba) or radium (Ra). The P-type charge generation layer may be formed of an organic layer obtained by doping an organic host material having a hole transporting capacity with dopant.

The second electrode **263** is provided on the organic light emitting layer **262**. The second electrode **263** may also be referred to as an upper electrode. The second electrode **263** is a common layer provided on the subpixels (P1, P2, P3) in common. The second electrode **263** may be formed of a conductive film, and more specifically a metal film. In one embodiment, the second electrode **263** is formed of a transparent metal material (transparent conductive material, TCO) capable of transmitting light therethrough, for example, Indium Tin Oxide (ITO) or Indium Zinc Oxide (IZO). A capping layer may be provided on the second electrode **263**.

The photo-reactive organic film **280** is provided on the second electrode **263**. As shown in FIG. 5, the photo-reactive organic film **280** includes diarylethene molecules, whereby it has the photo-isomerization properties. For example, the photo-reactive organic film **280** may be formed in a structure obtained by combining a host organic material with diarylethene molecules. The host organic material may be organoboron molecules obtained by combining boron with carbon such as BMB-2T, oxadiazole molecules such as PBD, azole-based molecules such as TAZ or TPBI, triazole molecules, or silole-based molecules.

As shown in FIG. 5, if the diarylethene molecules are irradiated with ultraviolet rays (hereinafter, referred to as "UV"), its structure is changed from an open-ring structure into a close-ring structure. Meanwhile, if the diarylethene molecules are irradiated with visible rays (hereinafter, referred to as "VR"), its structure is changed from the close-ring structure into the open-ring structure.

If the diarylethene molecules have the open-ring structure, the photo-reactive organic film **280** has a hydrophobic property by a large amount of fluorine. Thus, if the diarylethene molecules have the open-ring structure, an adhesion property between the photo-reactive organic film **280** and a conductive film, such as a metal film, is not good so that it is difficult to deposit the conductive film on the photo-reactive organic film **280**.

If the diarylethene molecules have the close-ring structure, the fluorine molecules in the surface of the photo-reactive organic film **280** are arranged inside the photo-reactive organic film **280**. Thus, the surface of the photo-reactive organic film **280** has a hydrophilic property, whereby the conductive film is easily deposited on the photo-reactive organic film **280**.

If using the photo-isomerization properties in the diarylethene molecules of the photo-reactive organic film **280**, the conductive film may be selectively provided on predetermined areas. Accordingly, the areas of the first to third subpixels (P1, P2, P3) are irradiated with UV, and a first

conductive film corresponding to a first optical auxiliary layer **281** is deposited on the area corresponding to the first subpixel (P1), a second conductive film corresponding to a second optical auxiliary layer **282** is deposited on the area corresponding to the second subpixel (P2), and a third conductive film corresponding to a third optical auxiliary layer **283** is deposited on the area corresponding to the third subpixel (P3). The first optical auxiliary layer **281** may be disposed above the first part of the organic light emitting layer **262** in the first subpixel P1, the second optical auxiliary layer **282** may be disposed above the second part of the organic light emitting layer **262** in the second subpixel P2, and the third optical auxiliary layer **283** may be disposed above the third part of the organic light emitting layer **263** in the third subpixel P3.

In one embodiment referred throughout the remainder of the specification, the first optical auxiliary layer **281**, the second optical auxiliary layer **282**, and the third optical auxiliary layer **283** may be formed of a metal film. The first to third optical auxiliary layers **281**, **282**, and **283** may be formed of a transparent metal material (transparent conductive material, TCO) capable of transmitting light there-through, for example, Indium Tin Oxide (ITO) or Indium Zinc Oxide (IZO). However, it is appreciated that in other embodiments, the optical auxiliary layers can be a conductive film other than a metal film.

Also, it is possible to adjust a thickness of the metal film deposited on the photo-reactive organic film **280** in accordance with an amount of UV irradiation. As the amount of UV irradiation is increased, the thickness of the metal film deposited on the photo-reactive organic film **280** becomes thicker. Thus, if the amount of UV irradiation applied to the photo-reactive organic film **280** overlapping with the third subpixel (P3) is the largest, and the amount of UV irradiation applied to the photo-reactive organic film **280** overlapping with the first subpixel (P1) is the smallest, the thickness of the third optical auxiliary layer **283** is the largest, and the thickness of the first optical auxiliary layer **281** is the smallest. That is, the first optical auxiliary layer **281**, the second optical auxiliary layer **282**, and the third optical auxiliary layer **283** may have the different thicknesses from one another.

A semi-transmissive electrode **290** is provided on the photo-reactive organic film **280**, and the first to third optical auxiliary layers **281**, **282**, and **283**. The semi-transmissive electrode **290** may be formed of a semi-transmissive conductive material such as magnesium (Mg), argentums (Ag), or alloy of magnesium (Mg) and argentums (Ag). Specifically, a first part of the semi-transmissive electrode **290** may be disposed on the first optical auxiliary layer **281**, a second part of the semi-transmissive electrode **290** may be disposed on the second optical auxiliary layer **282**, and a third part of the semi-transmissive electrode **290** may be disposed on the third optical auxiliary layer **283**.

According to the embodiment of the present disclosure, the first electrode **261** is formed of the metal material with high reflectance, and the semi-transmissive electrode **290** is formed of the semi-transmissive metal material, whereby it is possible to realize a micro-cavity structure by the first electrode **261** and the semi-transmissive electrode **290**, to thereby improve an emission efficiency of light emitted from the organic light emitting layer **262**. Herein, the micro-cavity indicates that the light-emission efficiency is improved by amplification and constructive interference of the light through repetitive reflection and re-reflection of the

light, which is emitted from the organic light emitting layer **262**, between the first electrode **261** and the semi-transmissive electrode **290**.

According to the embodiment of the present disclosure, the first optical auxiliary layer **281** of the first subpixel (P1), the second optical auxiliary layer **282** of the second subpixel (P2), and the third optical auxiliary layer **283** of the third subpixel (P3) have the different thicknesses from one another, whereby it is possible to optimize a micro-cavity distance in each of the first to third subpixels (P1, P2, P3). The second electrode **263** is disposed between the first optical auxiliary layer **281** and the first part of the organic light emitting layer **262**, between the second optical auxiliary layer **282** and the second part of the organic light emitting layer **262**, and between the third optical auxiliary layer **283** and the third part of the organic light emitting layer **263**. The photo-reactive organic film **280** is disposed between the first optical auxiliary layer **281** and the second electrode **263**, between the second optical auxiliary layer **282** and the second electrode **263**, and between the third optical auxiliary layer **283** and the second electrode **263**.

An encapsulation film **300** is provided on the semi-transmissive electrode **290**. The encapsulation film **300** may prevent permeation of oxygen or moisture into the organic light emitting layer **262** and the second electrode **263**. The encapsulation film **300** may include at least one inorganic film. The inorganic film may be formed of silicon nitride, aluminum nitride, zirconium nitride, titanium nitride, hafnium nitride, tantalum nitride, silicon oxide, aluminum oxide, or titanium oxide.

Also, the encapsulation film **300** may include at least one organic film. The organic film may be formed at a thickness enough to prevent particles from getting into the organic light emitting layer **262** and the second electrode **263** through the encapsulation film **300**.

The color filters **311**, **312**, and **313** are provided on the encapsulation film **300**. If the color filters **311**, **312**, and **313** are provided on the encapsulation film **300**, there is no need for an alignment process when the first and second substrates **111** and **112** are bonded to each other, whereby it is possible to reduce a thickness of the display panel since there is no need for an additional adhesion layer.

The color filters **311**, **312**, and **313** may be disposed in the respective subpixels (P1, P2, P3). For example, as shown in FIG. 4, the first color filter **311** is disposed in the first subpixel (P1), the second color filter **312** is disposed in the second subpixel (P2), and the third color filter **313** is disposed in the third subpixel (P3). The black matrix **320** is disposed between each of the color filters **311**, **312**, and **313**.

An overcoat layer may be provided on the color filters **311**, **312**, and **313** so as to planarize a step difference area caused by the color filters **311**, **312**, and **313** and the black matrix **320**. The second substrate **112** is disposed on the color filters **311**, **312**, and **313**. The second substrate **112** may be a plastic film, a glass substrate, or an encapsulation film (protection film).

According to the embodiment of the present disclosure, the first electrode **261** is formed of the metal material with high reflectance, and the semi-transmissive electrode **290** is formed of the semi-transmissive metal material, whereby it is possible to realize the micro-cavity structure by the first electrode **261** and the semi-transmissive electrode **290**, to thereby improve the emission efficiency of light emitted from the organic light emitting layer **262**. Also, the first optical auxiliary layer **281** of the first subpixel (P1), the second optical auxiliary layer **282** of the second subpixel (P2), and the third optical auxiliary layer **283** of the third

subpixel (P3) have the different thicknesses from one another, whereby it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3).

In this embodiment of the present disclosure, the thickness of the first optical auxiliary layer **281** is the smallest, and the thickness of the third optical auxiliary layer **283** is the largest, but not limited to this structure. That is, the thickness of each of the first to third optical auxiliary layers **281**, **282**, and **283** may be designed in an optimum range through a pretest in consideration of a wavelength of the light emitted from the subpixels, and a distance between the first electrode **261** and the semi-transmissive electrode **290**.

FIG. 6 is a flow chart illustrating a method for manufacturing an OLED device according to one embodiment of the present disclosure. FIGS. 7A to 7D are cross sectional views illustrating the method for manufacturing the OLED device according to one embodiment of the present disclosure.

The cross sectional views shown in FIGS. 7A to 7D relate to the method for manufacturing the OLED device shown in FIG. 4, whereby the same reference numbers will be used throughout the drawings to refer to the same or like parts. Hereinafter, the method for manufacturing the OLED device according to one embodiment of the present invention will be described with reference to FIGS. 6 and 7A to 7D.

First, as shown in FIG. 7A, the thin film transistors **210**, the organic light emitting device **260**, and the photo-reactive organic film **280** are provided, as indicated in S101 of FIG. 6.

In detail, before forming the thin film transistor **210**, the buffer film may be provided on the first substrate **111** so as to protect the thin film transistor **210** and the organic light emitting device **260** from the moisture permeating through the first substrate **111** which is vulnerable to the moisture. The buffer film may be formed of the plurality of inorganic films deposited alternately. For example, the buffer film may be formed in a multi-layered structure by alternately depositing at least one inorganic film from a silicon oxide film (SiOx), a silicon nitride film (SiNx), and silicon oxynitride (SiON). The buffer film may be formed by a chemical vapor deposition (CVD) method.

Thereafter, the active layer **211** of the thin film transistor **210** is provided on the buffer film. In detail, an active metal layer is provided on an entire surface of the buffer film by sputtering or metal organic chemical vapor deposition (MOCVD) method, and then the active metal layer is patterned by a mask process using a photoresist pattern, to thereby form the active layer **211**. The active layer **211** may be formed of a silicon-based semiconductor material or an oxide-based semiconductor material.

Then, the gate insulating film **220** is provided on the active layer **211**. The gate insulating film **220** may be formed in a single-layered structure of the inorganic insulating material such as silicon oxide (SiOx) or silicon nitride (SiNx), or a multi-layered structure of the above silicon oxide (SiOx) and silicon nitride (SiNx).

Then, the gate electrode **212** of the thin film transistor **210** is provided on the gate insulating film **220**. In detail, a first metal layer is provided on an entire surface of the gate insulating film **220** by sputtering or MOCVD method, and then the first metal layer is patterned by a mask process using a photoresist pattern, to thereby form the gate electrode **212**. The gate electrode **212** may be formed in a single-layered structure or multi-layered structure among molybdenum (Mo), aluminum (Al), chrome (Cr), aurum (Au), titanium (Ti), nickel (Ni), neodymium (Nd), copper (Cu) and their alloys.

The insulating interlayer **230** is provided on the gate electrode **212**. The insulating interlayer **230** may be formed in a single-layered structure of the inorganic insulating material such as silicon oxide (SiOx) or silicon nitride (SiNx), or a multi-layered structure of the above silicon oxide (SiOx) and silicon nitride (SiNx).

Then, the contact holes for exposing the active layer **211** are provided through the gate insulating film **220** and the insulating interlayer **230**.

The source and drain electrodes **214** and **215** of the thin film transistor **210** are provided on the insulating interlayer **230**. In detail, a second metal layer is provided on an entire surface of the insulating interlayer **230** by sputtering or MOCVD method. Then, the second metal layer is patterned by a mask process using a photoresist pattern. Each of the source and drain electrodes **214** and **215** may be connected with the active layer **211** via the contact hole penetrating through the gate insulating film **220** and the insulating interlayer **230**. Each of the source and drain electrodes **214** and **215** may be formed in a single-layered structure or multi-layered structure among molybdenum (Mo), aluminum (Al), chrome (Cr), aurum (Au), titanium (Ti), nickel (Ni), neodymium (Nd), copper (Cu) and their alloys.

Then, the protection film **240** is provided on the source and drain electrodes **214** and **215** of the thin film transistor **210**. The protection film **240** may be formed in a single-layered structure of the inorganic insulating material such as silicon oxide (SiOx) or silicon nitride (SiNx), or a multi-layered structure of the above silicon oxide (SiOx) and silicon nitride (SiNx). The protection film **240** may be formed by the CVD method.

Then, the planarization film **250** may be provided on the protection film **240** so as to planarize the step difference area caused by the thin film transistor **210**. The planarization film **250** may be formed of an organic material, for example, acryl resin, epoxy resin, phenolic resin, polyamide resin, polyimide resin, and etc.

Then, the first electrode **261** of the organic light emitting device **260** is provided on the planarization film **250**. In detail, a third metal film is provided on an entire surface of the planarization film **250** by sputtering or MOCVD method, and then the third metal film is patterned by a mask process using a photoresist pattern, to thereby provide the first electrode **261**. The first electrode **261** may be connected with the source electrode **214** of the thin film transistor **210** via the contact hole penetrating through the protection film **240** and the planarization film **250**. The first electrode **261** may be formed of a metal material with high reflectance, and more particularly, a deposition structure of aluminum and titanium (Ti/Al/Ti), a deposition structure of aluminum and Indium Tin Oxide (ITO/Al/ITO), an APC alloy, and a deposition structure of APC alloy and Indium Tin Oxide (ITO/APC/ITO).

Then, the bank **270** is provided to cover the edge of the first electrode **261** on the planarization film **250**, to thereby divide the subpixels (P1, P2, P3). The bank **270** may be formed of an organic material, for example, acryl resin, epoxy resin, phenolic resin, polyamide resin, polyimide resin, and etc.

Then, the organic light emitting layer **262** is provided on the first electrode **261** and the bank **270** by a deposition process or solution process. The organic light emitting layer **262** is a common layer provided on the subpixels (P1, P2, P3) in common. In this case, the organic light emitting layer may be a white light emitting layer for emitting white light.

If the organic light emitting layer **262** is the white light emitting layer, it may have a tandem structure of 2 stacks or

more than 2 stacks. Each stack may include a hole transporting layer, at least one light emitting layer, and an electron transporting layer.

Between each of the stacks, there may be a charge generation layer. The charge generation layer may include an n-type charge generation layer positioned adjacent to the lower stack, and a p-type charge generation layer provided on the n-type charge generation layer and positioned adjacent to the upper stack. The n-type charge generation layer injects the electron into the lower stack, and the p-type charge generation layer injects the hole into the upper stack. The n-type charge generation layer may be formed of an organic layer doped with alkali metal such as lithium (Li), sodium (Na), potassium (K) or cesium (Cs), or alkali earth metal such as magnesium (Mg), strontium (Sr), barium (Ba) or radium (Ra). The p-type charge generation layer may be formed of an organic layer obtained by doping an organic host material having a hole transporting capacity with dopant.

The second electrode **263** is provided on the organic light emitting layer **262**. The second electrode **263** may be a common layer provided on the subpixels (P1, P2, P3) in common. The second electrode **263** may be formed of a transparent metal material (transparent conductive material, TCO) capable of transmitting light therethrough, for example, Indium Tin Oxide (ITO) or Indium Zinc Oxide (IZO). The second electrode **263** may be formed of a physical vapor deposition method such as sputtering. The capping layer may be provided on the second electrode **263**.

Then, the photo-reactive organic film **280** is provided on the second electrode **263**. The photo-reactive organic film **280** may be a common layer provided on the subpixels (P1, P2, P3) in common. The photo-reactive organic film **280** includes diarylethene molecules, as shown in FIG. 5, whereby it has the photo-isomerization properties. As shown in FIG. 5, if the diarylethene molecules are irradiated with ultraviolet rays (hereinafter, referred to as "UV"), its structure is changed from an open-ring structure into a close-ring structure. Meanwhile, if the diarylethene molecules are irradiated with visible rays (hereinafter, referred to as "VR"), its structure is changed from the close-ring structure into the open-ring structure.

If the diarylethene molecules have the open-ring structure, the photo-reactive organic film **280** has a hydrophobic property by a large amount of fluorine. Thus, if the diarylethene molecules have the open-ring structure, an adhesion property between the photo-reactive organic film **280** and the metal film is not good so that it is difficult to deposit the metal film on the photo-reactive organic film **280**.

If the diarylethene molecules have the close-ring structure, the fluorine molecules in the surface of the photo-reactive organic film **280** are arranged inside the photo-reactive organic film **280**. Thus, the surface of the photo-reactive organic film **280** has a hydrophilic property, whereby the metal film is easily deposited on the photo-reactive organic film **280**.

Second, as shown in FIG. 7B, the photo-reactive organic film **280** is irradiated with UV under a first mask (M1) having transmitting portions (T1, T2, T3) with different UV transmittances, as indicated in S102 of FIG. 6.

In detail, the first mask (M1) is provided with the first transmitting portion (T1) having the first UV transmittance, the second transmitting portion (T2) having the second UV transmittance which is higher than the first UV transmittance, and the third transmitting portion (T3) having the third UV transmittance which is higher than the second UV transmittance. The photo-reactive organic film **280** is irradiated

with UV under the first mask (M1). For example, the first transmitting portion (T1) is positioned above the first subpixel (P1), the second transmitting portion (T2) is positioned above the second subpixel (P2), and the third transmitting portion (T3) is positioned above the third subpixel (P3). In this case, the amount of UV irradiation for the third subpixel (P3) is the largest, and the amount of UV irradiation for the first subpixel (P1) is the smallest.

Third, as shown in FIG. 7C, the first optical auxiliary layer **281** having a first thickness is provided in the first subpixel (P1), the second optical auxiliary layer **282** having a second thickness is provided in the second subpixel (P2), and the third optical auxiliary layer **283** having a third thickness is provided in the third subpixel (P3), as indicated in S103 of FIG. 6.

In detail, the metal film is deposited only on the area irradiated with UV, and the metal film is not deposited on the area which is not irradiated with UV. Accordingly, even though an open mask having a transmitting portion for the display area is used instead of a mask having transmitting portions for the first to third subpixels (P1, P2, P3), the first to third optical auxiliary layers **281**, **282**, and **283** may be deposited on the photo-reactive organic film **280** of the first to third subpixels (P1, P2, P3) irradiated with UV. That is, the first optical auxiliary layer **281** may be deposited on the first subpixel (P1), the second optical auxiliary layer **282** may be deposited on the second subpixel (P2), and the third optical auxiliary layer **283** may be deposited on the third subpixel (P3).

Also, it is possible to adjust the thickness of the metal film deposited on the photo-reactive organic film **280** in accordance with the amount of UV irradiation. As the amount of UV irradiation is increased, the thickness of the metal film deposited on the photo-reactive organic film **280** becomes thicker. The amount of UV irradiation applied to the third subpixel (P3) is the largest, and the amount of UV irradiation applied to the first subpixel (P1) is the smallest. Thus, as shown in FIG. 7C, the thickness of the third optical auxiliary layer **283** deposited on the third subpixel (P3) is the largest, and the thickness of the first optical auxiliary layer **281** deposited on the first subpixel (P1) is the smallest. Due to the difference in the amount of UV irradiation between the first transmitting portion T1, the second transmitting portion T2, and the third transmitting portion T3, the hydrophobicity of a first portion of the photo-reactive organic film **280** below the first optical auxiliary layer **281** may be larger than a hydrophobicity of a second portion of the photo-reactive organic film **280** below the second optical auxiliary layer **282**. The hydrophobicity of the second portion of the photo-reactive organic film **280** may be larger than a hydrophobicity of a third portion of the photo-reactive organic film **280** below the third optical auxiliary layer **283**. The hydrophobicity of the first portion, the second portion, and the third portion of the organic film **280** may be smaller than a portion of the organic film **280** that does not overlap with the optical auxiliary layers **281**, **282**, and **283**. As the hydrophobicity of the photo-reactive organic film **280** is larger, the photo-reactive organic film **280** may not be mixed with water. In this case, the contact angle of a water droplet on the surface of the photo-reactive organic film **280** may exceed 90°. If the contact angle of the water droplet exceeds 150°, the photo-reactive organic film **280** may have a superhydrophobic surface. As the hydrophilicity of the photo-reactive organic film **280** is larger, the photo-reactive organic film **280** may be mixed with water. In this case, the contact angle of the water droplet on the surface of the photo-reactive organic film **280** may not exceed 90°. If the

contact angle of the water droplet does not exceed 20°, the photo-reactive organic film **280** may have a super-hydrophilic surface. The hydrophobicity of the photo-reactive organic film **280** may be measured by the contact angle of the water droplet on the surface of the photo-reactive organic film **280**.

As described above, the first optical auxiliary layer **281** of the first subpixel (P1), the second optical auxiliary layer **282** of the second subpixel (P2), and the third optical auxiliary layer **283** of the third subpixel (P3) may have the different thicknesses from one another by adjusting the amount of UV irradiation applied to the first to third subpixels (P1, P2, P3). Thus, it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3).

Fourth, as shown in FIG. 7D, the semi-transmissive electrode **290** and the encapsulation film **300** are provided on the photo-reactive organic film **280**, and the first to third optical auxiliary layers **281**, **282**, and **283**, as indicated in S104 of FIG. 6.

In detail, the semi-transmissive electrode **290** is provided on the photo-reactive organic film **280**, and the first to third optical auxiliary layers **281**, **282**, and **283**. The semi-transmissive electrode **290** may be formed of a semi-transmissive conductive material such as magnesium (Mg), argentums (Ag), or alloy of magnesium (Mg) and argentums (Ag).

Then, the encapsulation film **300** is provided on the semi-transmissive electrode **290**. The encapsulation film **300** may prevent a permeation of oxygen or moisture into the organic light emitting layer **262** and the second electrode **263**. The encapsulation film **300** may include at least one inorganic film. The inorganic film may be formed of silicon nitride, aluminum nitride, zirconium nitride, titanium nitride, hafnium nitride, tantalum nitride, silicon oxide, aluminum oxide, or titanium oxide.

Also, the encapsulation film **300** may further include at least one organic film. The organic film may be formed at a thickness enough to prevent particles from getting into the organic light emitting layer **262** and the second electrode **263** through the encapsulation film **300**.

The black matrix **320** and the color filters **311**, **312**, and **313** are provided on the encapsulation film **300**. If the black matrix **320** and the color filters **311**, **312**, and **313** are directly provided on the encapsulation film **300**, there is no need for an alignment process when the first and second substrates **111** and **112** are bonded to each other, whereby it is possible to reduce the thickness of the display panel since there is no need for the additional adhesion layer, in comparison to a case of forming the black matrix **320** and the color filters **311**, **312**, and **313** on the second substrate **112**, and bonding to the first and second substrates **111** and **112** to each other.

The color filters **311**, **312**, and **313** may be disposed in the respective subpixels (P1, P2, P3). For example, as shown in FIG. 7D, the first color filter **311** is disposed in the first subpixel (P1), the second color filter **312** is disposed in the second subpixel (P2), and the third color filter **313** is disposed in the third subpixel (P3).

The overcoat layer may be provided on the color filters **311**, **312**, and **313** so as to planarize the step difference area caused by the color filters **311**, **312**, and **313** and the black matrix **320**.

Then, the second substrate **112** is attached onto the color filters **311**, **312**, and **313**. The second substrate **112** may be a plastic film, a glass substrate, or an encapsulation film (protection film).

As described above, under the condition that the mask is disposed on the photo-reactive organic film **280**, the photo-reactive organic film **280** is irradiated with UV by the use of

first mask (M1) having transmitting portions with different UV transmittances so that the thickness of the first optical auxiliary layer **281** of the first subpixel (P1), the thickness of the second optical auxiliary layer **282** of the second subpixel (P2), and the thickness of the third optical auxiliary layer **283** of the third subpixel (P3) may be different from one another. As a result, it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3) by the three processes including the deposition process of the photo-reactive organic film **280**, the UV irradiation process, and the deposition process of the metal film. Accordingly, it is possible to largely reduce the number of manufacturing processes, to thereby simplify the manufacturing process, and to reduce a manufacturing cost.

FIG. 8 is a flow chart illustrating a method for manufacturing an OLED device according to another embodiment of the present disclosure. FIGS. 9A to 9H are cross sectional views illustrating the method for manufacturing the OLED device according to another embodiment of the present disclosure.

The cross sectional views shown in FIGS. 9A to 9H relate to the method for manufacturing the above OLED device shown in FIG. 4, whereby the same reference numbers will be used throughout the drawings to refer to the same or like parts. Hereinafter, the method for manufacturing the OLED device according to another embodiment of the present disclosure will be described in detail with reference to FIG. 8 and FIGS. 9A to 9H.

First, as shown in FIG. 9A, the thin film transistors **210**, the organic light emitting devices **260**, and the photo-reactive organic film **280** are provided, as indicated in S201 of FIG. 8.

The step S201 of FIG. 8 is the same as the step S101 of FIG. 6, whereby a detailed description for the step S201 of FIG. 8 will be omitted ('S201' of FIG. 8) for sake of brevity.

Second, as shown in FIGS. 9B and 9C, a metal film **283'** is formed by irradiating the area for the third subpixel (P3) with UV, as indicated in S202 of FIG. 8.

In detail, as shown in FIG. 9B, under the condition that a second mask (M2) having a transmitting portion (T) is disposed on the photo-reactive organic film **280**, the photo-reactive organic film **280** is irradiated with UV. In this case, the transmitting portion (T) is positioned above the area for the third subpixel (P3). The first and second subpixels (P1, P2) are not irradiated with UV, and only the third subpixel (P3) is irradiated with UV.

As shown in FIG. 5, the photo-reactive organic film **280** includes diarylethene molecules. Thus, the metal film is deposited only on the area of the photo-reactive organic film **280** which is irradiated with UV, and the metal film is not deposited on the area of the photo-reactive organic film **280** which is not irradiated with UV. Accordingly, even though an open mask having a transmitting portion for the display area is used instead of a mask having transmitting portions for the third subpixel (P3), the metal film **283'** may be deposited only on the third subpixel (P3).

Third, as shown in FIGS. 9D and 9E, the area for the second subpixel (P2) is irradiated with UV, to thereby form metal films **282'** and **283''**, as indicated in S203 of FIG. 8.

In detail, as shown in FIG. 9D, under the condition that a third mask (M3) having a transmitting portion (T) is disposed on the photo-reactive organic film **280**, the photo-reactive organic film **280** is irradiated with UV. In this case, the transmitting portion (T) is positioned above the area for the second subpixel (P2). The first and third subpixels (P1, P3) are not irradiated with UV, and only the second subpixel (P2) is irradiated with UV.

As shown in FIG. 5, the photo-reactive organic film **280** includes diarylethene molecules. Thus, the metal film is deposited only on the area of the photo-reactive organic film **280** which is irradiated with UV, and the metal film is not deposited on the area of the photo-reactive organic film **280** which is not irradiated with UV. Accordingly, even though an open mask having a transmitting portion for the display area is used instead of a mask having transmitting portions for the second and third subpixels (P2, P3), as shown in FIG. 9E, the metal films **282'** and **283''** may be deposited on the second and third subpixels (P2, P3) irradiated with UV.

Fourth, as shown in FIGS. 9F and 9G, the area for the first subpixel (P1) is irradiated with UV, to thereby form the first to third optical auxiliary layers **281**, **282**, and **283**, as indicated in S204 of FIG. 8.

In detail, as shown in FIG. 9F, under the condition that a fourth mask (M4) having a transmitting portion (T) is disposed on the photo-reactive organic film **280**, the photo-reactive organic film **280** is irradiated with UV. In this case, the transmitting portion (T) is positioned above the area for the first subpixel (P1). The second and third subpixels (P2, P3) are not irradiated with UV, and only the first subpixel (P1) is irradiated with UV.

As shown in FIG. 5, the photo-reactive organic film **280** includes diarylethene molecules. Thus, the metal film is deposited only on the area of the photo-reactive organic film **280** which is irradiated with UV, and the metal film is not deposited on the area of the photo-reactive organic film **280** which is not irradiated with UV. Accordingly, even though an open mask having a transmitting portion for the display area is used instead of a mask having transmitting portions for the first to third subpixels (P1, P2, P3), as shown in FIG. 9G, the first to third optical auxiliary layers **281**, **282**, and **283** may be deposited on the first to third subpixels (P1, P2, P3) irradiated with UV. When the transmittance of the second mask M2, third mask M3, and the fourth mask M4 are substantially similar, a hydrophobicity of a first portion of the photo-reactive organic film **280** below the first optical auxiliary layer **281**, a hydrophobicity of a second portion of the photo-reactive organic film **280** below the second optical auxiliary layer **282**, and a hydrophobicity of a third portion of the photo-reactive organic film **280** below the third optical auxiliary layer **283** may be substantially same with one another. As the hydrophobicity of the photo-reactive organic film **280** is larger, the photo-reactive organic film **280** may not be mixed with water. In this case, the contact angle of a water droplet on the surface of the photo-reactive organic film **280** may exceed 90°. If the contact angles of the water droplet exceeds 150°, the photo-reactive organic film **280** may have super-hydrophobic surface. As the hydrophilicity of the photo-reactive organic film **280** is larger, the photo-reactive organic film **280** may be mixed with water. In this case, the contact angle of the water droplet on the surface of the photo-reactive organic film **280** may not exceed 90°. If the contact angles of the water droplet does not exceed 20°, the photo-reactive organic film **280** may have super-hydrophilic surface. The hydrophobicity of the photo-reactive organic film **280** may be measured by the contact angle of the water droplet on the surface of the photo-reactive organic film **280**. The hydrophobicity of the first portion, the second portion, and the third portion of the photo-reactive organic film **280** may be smaller than a hydrophobicity of a portion of the organic film **280** that does not overlap with the optical auxiliary layers **281**, **282**, and **283**.

Meanwhile, the metal film is deposited on the photo-reactive organic film **280** of the third subpixel (P3) by the steps of S202, S203, and S204, the metal film is deposited

on the photo-reactive organic film **280** of the second subpixel (P2) by the steps of S203 and S204, and the metal film is deposited on the photo-reactive organic film **280** of the first subpixel (P1) by the steps of S204. Accordingly, the third optical auxiliary layer **283** of the third subpixel (P3) has the largest thickness, and the first optical auxiliary layer **281** of the first subpixel (P1) has the smallest thickness. That is, the thickness of the first optical auxiliary layer **281**, the thickness of the second optical auxiliary layer **282**, and the thickness of the third optical auxiliary layer **283** may be different from one another.

Fifth, as shown in FIG. 9H, the semi-transmissive electrode **290** and the encapsulation film **300** are provided on the photo-reactive organic film **280**, and the first to third optical auxiliary layers **281**, **282**, and **283**, as indicated in S205 of FIG. 8.

The step S205 of FIG. 8 is the same as the step S104 of FIG. 6, whereby a detailed description for the step S205 of FIG. 8 will be omitted ('S205' of FIG. 8) for the sake of brevity.

As described above, after the metal film **283'** is deposited by irradiating the area for the third subpixel (P3) with UV, the metal film **282'** and **283''** is deposited by irradiating the area for the second subpixel (P2) with UV, and then the first to third optical auxiliary layers **281**, **282**, and **283** are deposited by irradiating the area for the first subpixel (P1) with UV. As a result, the thickness of the first optical auxiliary layer **281** in the first subpixel (P1), the thickness of the second optical auxiliary layer **282** in the second subpixel (P2), and the thickness of the third optical auxiliary layer **283** in the third subpixel (P3) may be different from one another. As a result, it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3) by the seven processes including the deposition process of the photo-reactive organic film **280**, the three UV irradiation processes, and the three deposition processes of the metal film. Accordingly, it is possible to largely reduce the number of manufacturing processes, to simplify the manufacturing process, and to reduce a manufacturing cost.

FIG. 10 is a cross sectional view showing another example along I-I' of FIG. 3 according to an embodiment of the present disclosure.

Except that the second electrodes **263a**, **263b**, and **263c** of the first to third subpixels (P1, P2, P3) have the different thicknesses instead of the first to third optical auxiliary layers **281**, **282**, and **283**, the cross sectional view shown in FIG. 10 is identical to the above cross sectional view shown in FIG. 4. In FIG. 10, a detailed description for the first substrate **111**, the thin film transistor **210**, the gate insulating film **220**, the insulating interlayer **230**, the protection film **240**, the planarization film **250**, the first electrodes **261**, the bank **270**, the encapsulation film **300**, the color filters **311**, **312**, and **313**, the black matrix **320**, and the second substrate **112** will be omitted for the sake of brevity.

Referring to FIG. 10, the organic light emitting layer **262** is provided on the first electrode **261** and the bank **270**. The organic light emitting layer **262** is a common layer provided on the subpixels (P1, P2, P3) in common. The organic light emitting layer **262** may be a white light emitting layer for emitting white light. In this case, the organic light emitting layer **262** may have a tandem structure of 2 stacks or more than 2 stacks, as shown in FIG. 11. FIG. 11 shows that the organic light emitting layer **262** includes two stacks **262a** and **262b**, but not limited to this structure. That is, the organic light emitting layer **262** may include three or more stacks. Between the stacks **262a** and **262b**, there is a charge generation layer **262c**. Each subpixel may include a corre-

sponding part of the organic light emitting layer **262** disposed on the first electrode **261** of the subpixel. Thus, the first subpixel **P1** may include at least a first part of the organic light emitting layer **262** on the first electrode **261** of the first subpixel **P1**, the second subpixel **P2** may include at least a second part of the organic light emitting layer **262** on the first electrode **261** of the second subpixel **P2**, and the third subpixel **P3** may include at least a third part of the organic light emitting layer **262** on the first electrode **261** of the third subpixel **P3**.

Referring to FIG. **11**, the first stack **262a** includes a first hole transporting layer (**HTL1**), a first light emitting layer (**EL1**), and a first electron transporting layer (**ETL1**). The second stack **262b** includes a second hole transporting layer (**HTL2**), a second light emitting layer (**EL2**), and the photo-reactive organic film **280**.

The first hole transporting layer (**HTL1**) transfers the hole injected from the first electrode **261** to the first light emitting layer (**EL1**). The second hole transporting layer (**HTL2**) transfers the hole injected from the charge generation layer **262c** to the second light emitting layer (**EL2**). Each of the first hole transporting layer (**HTL1**) and the second hole transporting layer (**HTL2**) may be formed of NPD(**N,N**-dinaphthyl-**N,N'**-diphenyl benzidine), TPD(**N,N'**-bis-(3-methylphenyl)-**N,N'**-bis-(phenyl)-benzidine), TCTA(4-(9H-carbazol-9-yl)-**N,N**-bis[4-(9H-carbazol-9-yl)phenyl]-benzenamine), CBP(4,4'-**N,N'**-dicarbazole-biphenyl), s-TAD, or MTDATA(4,4',4''-Tris(**N**-3-methylphenyl-**N**-phenyl-amino)-triphenylamine), but not limited to these materials.

Each of the first light emitting layer (**EL1**) and the second light emitting layer (**EL2**) includes host and dopant. Also, each of the first light emitting layer (**EL1**) and the second light emitting layer (**EL2**) may include a material for emitting predetermined-colored light, which may be formed of a phosphorescent or fluorescent material.

If each of the first light emitting layer (**EL1**) and the second light emitting layer (**EL2**) is an organic light emitting layer for emitting red light, it may include a host material of CBP(carbazole biphenyl) or mCP(1,3-bis(carbazol-9-yl)), and may include a phosphorescent material having dopant with at least any one selected among PIQIr(acac)(bis(1-phenylisoquinoline)acetylacetonate iridium), PQIr(acac)(bis(1-phenylquinoline)acetylacetonate iridium), PQIr(tris(1-phenylquinoline)iridium), and PtOEP(octaethylporphyrin platinum), or a fluorescent material having dopant with PBD:Eu(DBM)3(Phen) or Perylene, but not limited to these materials.

If each of the first light emitting layer (**EL1**) and the second light emitting layer (**EL2**) is an organic light emitting layer for emitting green light, it may include a host material of CBP or mCP, and may include a phosphorescent material having dopant with Ir(ppy)3(fac tris(2-phenylpyridine) iridium), or a fluorescent material having dopant with Alq3 (tris(8-hydroxyquinolino)aluminum), but not limited to these materials.

If each of the first light emitting layer (**EL1**) and the second light emitting layer (**EL2**) is an organic light emitting layer for emitting blue light, it may include a host material of CBP or mCP, and may include a phosphorescent material having dopant with (4,6-F2ppy)2Irpic or L2BD111, but not limited to these materials.

Each of the first light emitting layer (**EL1**) and the second light emitting layer (**EL2**) may emit yellow light, magenta light, or blue-green light in addition to the red light, the blue light, and the green light.

The first electron transporting layer (**ETL1**) is disposed on the organic light emitting layer **262c**, wherein the first electron transporting layer (**ETL1**) transfers the electron injected from the second electrode **263** to the organic light emitting layer **262c**. The first electron transporting layer (**ETL1**) may be formed of PBD(2-(4-biphenyl)-5-(4-tert-butylphenyl)-1,3,4-oxadiazole), TAZ(3-(4-biphenyl)-4-phenyl-5-tertbutylphenyl-1,2,4-triazole), Liq(8-hydroxyquinolinolato-lithium), BALq(Bis(2-methyl-8-quinolinolato)-4-(phenylphenolato)aluminium), or TPBi(2,2',2''-(1,3,5-benzinetriyl)-tris(1-phenyl-1-H-benzimidazole), but not limited to these materials.

The charge generation layer **262c** may include an n-type charge generation layer positioned adjacent to the lower stack, and a p-type charge generation layer provided on the n-type charge generation layer and positioned adjacent to the upper stack. The n-type charge generation layer injects the electron into the lower stack, and the p-type charge generation layer injects the hole into the upper stack. The n-type charge generation layer may be formed of an organic layer obtained by doping an organic host material having an electron transporting capacity with alkali metal such as lithium (Li), sodium (Na), potassium (K) or cesium (Cs), or alkali earth metal such as magnesium (Mg), strontium (Sr), barium (Ba) or radium (Ra). The P-type charge generation layer may be formed of an organic layer obtained by doping an organic host material having a hole transporting capacity with dopant.

The first stack **262a** further includes a first hole injecting layer between the first electrode **261** and the first hole transporting layer (**HTL1**), and may further include a first electron injecting layer between the first electron transporting layer (**ETL1**) and the second stack **262b**. The second stack **262b** further includes a second hole injecting layer between the charge generation layer **262c** and the second hole transporting layer (**HTL2**), and may further include a second electron transporting layer between the second light emitting layer (**EL2**) and the photo-reactive organic film **280**.

The photo-reactive organic film **280** is disposed on the organic light emitting layer **262c**, wherein the photo-reactive organic film **280** transfers the electron injected from the second electrode **263** to the organic light emitting layer **262c**. Also, the photo-reactive organic film **280** includes diarylethene molecules, as shown in FIG. **5**, whereby it has the photo-isomerization properties. The photo-reactive organic film **280** may be formed of an electron transporting material including diarylethene molecules. As shown in FIG. **5**, if the diarylethene molecules are irradiated with ultraviolet rays (hereinafter, referred to as "UV"), its structure is changed from an open-ring structure into a close-ring structure. Meanwhile, if the diarylethene molecules are irradiated with visible rays (hereinafter, referred to as "VR"), its structure is changed from the close-ring structure into the open-ring structure.

If the diarylethene molecules have the open-ring structure, the photo-reactive organic film **280** has a hydrophobic property by a large amount of fluorine. Thus, if the diarylethene molecules have the open-ring structure, an adhesion property between the photo-reactive organic film **280** and a conductive film, such as a metal film, is not good so that it is difficult to deposit the metal film on the photo-reactive organic film **280**.

If the diarylethene molecules have the close-ring structure, the fluorine molecules in the surface of the photo-reactive organic film **280** are arranged inside the photo-reactive organic film **280**. Thus, the surface of the photo-

23

reactive organic film **280** has a hydrophilic property, whereby the conductive film is easily deposited on the photo-reactive organic film **280**.

If using the photo-isomerization properties in the diarylethene molecules of the photo-reactive organic film **280**, the metal film may be selectively provided on predetermined areas. Accordingly, the areas of the first to third subpixels (P1, P2, P3) are irradiated with UV, it is possible to form the second electrodes **263a**, **263b**, and **263c** for the first to third subpixels (P1, P2, P3). The second electrodes **263a**, **263b**, and **263c** may contact the photo-reactive organic film **280** included in the organic light emitting layer **262**. The second electrode **263a** of the first subpixel P1, which is a first conductive film, may be disposed above the first part of the organic light emitting layer **262** in the first subpixel P1, the second electrode **263b** of the second subpixel P2, which is a second conductive film, may be disposed above the second part of the organic light emitting layer **262** in the second subpixel P2, and the second electrode **263c** of the third subpixel P3, which is a third conductive film, may be disposed above the third part of the organic light emitting layer **263** in the third subpixel P3.

Also, it is possible to adjust a thickness of the metal film deposited on the photo-reactive organic film **280** in accordance with an amount of UV irradiation. As the amount of UV irradiation is increased, the thickness of the metal film deposited on the photo-reactive organic film **280** becomes thicker. Thus, if the amount of UV irradiation applied to the area overlapped with the third subpixel (P3) is the largest, and the amount of UV irradiation applied to the area overlapped with the first subpixel (P1) is the smallest, the thickness of the second electrode **263c** for the third subpixel (P3) is the largest, and the thickness of the second electrode **263a** for the first subpixel (P1) is the smallest. That is, the second electrodes **263a**, **263b**, and **263c** for the respective first to third subpixels (P1, P2, P3) may have the different thicknesses from one another.

The semi-transmissive electrode **290** is provided on the photo-reactive organic film **280**, and the second electrodes **263a**, **263b**, and **263c**. The semi-transmissive electrode **290** may be formed of a semi-transmissive conductive material such as magnesium (Mg), argentums (Ag), or alloy of magnesium (Mg) and argentums (Ag). Thus, a first part of the semi-transmissive electrode **290** may be disposed on the second electrode **263a** of the first subpixel P1, a second part of the semi-transmissive electrode **290** may be disposed on the second electrode **263b** of the second subpixel P2, and a third part of the semi-transmissive electrode **290** may be disposed on the second electrode **263c** of the third subpixel P3.

According to the embodiment of the present disclosure, the first electrode **261** is formed of the metal material with high reflectance, and the semi-transmissive electrode **290** is formed of the semi-transmissive metal material, whereby it is possible to realize a micro-cavity structure by the first electrode **261** and the semi-transmissive electrode **290**, to thereby improve an emission efficiency of light emitted from the organic light emitting layer **262**.

According to the embodiment of the present disclosure, the second electrode **263a** of the first subpixel (P1), the second electrode **263b** of the second subpixel (P2), and the second electrode **263c** of the third subpixel (P3) have the different thicknesses from one another, whereby it is possible to optimize a micro-cavity distance in each of the first to third subpixels (P1, P2, P3).

According to the embodiment of the present disclosure, the second electrode **263a** of the first subpixel (P1) has the

24

smallest thickness, and the second electrode **263c** of the third subpixel (P3) has the largest thickness, but not limited to this structure. That is, the thickness in each of the second electrodes **263a**, **263b**, and **263c** may be designed in an optimum range through a pretest in consideration of a wavelength of the light emitted from the subpixels, and a distance between the first electrode **261** and the semi-transmissive electrode **290**.

FIG. **12** is a flow chart illustrating a method for manufacturing an OLED device according to another embodiment of the present disclosure. FIGS. **13A** to **13D** are cross sectional views illustrating the method for manufacturing the OLED device according to another embodiment of the present disclosure.

The cross sectional views shown in FIGS. **13A** to **13D** relate to the method for manufacturing the above OLED device shown in FIG. **10**, whereby the same reference numbers will be used throughout the drawings to refer to the same or like parts. Hereinafter, the method for manufacturing the OLED device according to another embodiment of the present invention will be described in detail with reference to FIG. **12** and FIGS. **13A** to **13D**.

First, as shown in FIG. **13A**, the thin film transistors **210**, anode electrodes **261**, and the organic light emitting layer **262** are provided, as indicated in S301 of FIG. **12**.

The step S301 of FIG. **12**, which is provided to form the thin film transistors **210** and the anode electrodes **261**, is the same as the step S101 of FIG. **6**, whereby a detailed description for the step S301 of FIG. **12** will be omitted.

The organic light emitting layer **262** is provided on the first electrode **261** and the bank **270** by a deposition process or solution process. The organic light emitting layer **262** is a common layer provided on the subpixels (P1, P2, P3) in common. In this case, the organic light emitting layer **262** may be a white light emitting layer for emitting white light.

If the organic light emitting layer **262** is the white light emitting layer, it may have a tandem structure of 2 stacks or more than 2 stacks. Between the stacks **261a** and **261b**, there is a charge generation layer **261c**. As shown in FIG. **11**, the first stack **262a** includes a first hole transporting layer (HTL1), a first light emitting layer (EL1), and a first electron transporting layer (ETL1). The second stack **262b** includes a second hole transporting layer (HTL2), a second light emitting layer (EL2), and the photo-reactive organic film **280**.

The photo-reactive organic film **280** transfers the electron injected from the second electrode **263** to the organic light emitting layer **262c**. Also, the photo-reactive organic film **280** includes diarylethene molecules, as shown in FIG. **5**, whereby it has the photo-isomerization properties. The photo-reactive organic film **280** may be formed of an electron transporting material including diarylethene molecules. As shown in FIG. **5**, if the diarylethene molecules are irradiated with ultraviolet rays (hereinafter, referred to as "UV"), its structure is changed from an open-ring structure into a close-ring structure. Meanwhile, if the diarylethene molecules are irradiated with visible rays (hereinafter, referred to as "VR"), its structure is changed from the close-ring structure into the open-ring structure.

If the diarylethene molecules have the open-ring structure, the photo-reactive organic film **280** has a hydrophobic property by a large amount of fluorine. Thus, if the diarylethene molecules have the open-ring structure, an adhesion property between the photo-reactive organic film **280** and the metal film is not good so that it is difficult to deposit the metal film on the photo-reactive organic film **280**.

If the diarylethene molecules have the close-ring structure, the fluorine molecules in the surface of the photo-reactive organic film **280** are arranged inside the photo-reactive organic film **280**. Thus, the surface of the photo-reactive organic film **280** has a hydrophilic property, whereby the metal film is easily deposited on the photo-reactive organic film **280**.

Second, as shown in FIG. 13B, the first to third subpixels (P1, P2, P3) are irradiated with UV by the use of first mask (M1) having transmitting portions (T1, T2, T3) with different UV transmittances, as indicated in S302 of FIG. 12.

In detail, the first mask (M1) is provided with the first transmitting portion (T1) having the first UV transmittance, the second transmitting portion (T2) having the second UV transmittance which is higher than the first UV transmittance, and the third transmitting portion (T3) having the third UV transmittance which is higher than the second UV transmittance. The organic light emitting layer **262** is irradiated with UV under the first mask (M1). For example, the first transmitting portion (T1) is positioned in the first subpixel (P1), the second transmitting portion (T2) is positioned in the second subpixel (P2), and the third transmitting portion (T3) is positioned in the third subpixel (P3). In this case, the amount of UV irradiation for the third subpixel (P3) is the largest, and the amount of UV irradiation for the first subpixel (P1) is the smallest.

Third, as shown in FIG. 13C, the second electrode **263a** of the first pixel P1 having a first thickness is provided in the first subpixel (P1), the second electrode **263b** of the second pixel P2 having a second thickness is provided in the second subpixel (P2), and the second electrode **263c** of the third pixel P3 having a third thickness is provided in the third subpixel (P3), as indicated in S303 of FIG. 12.

Also, it is possible to adjust a thickness in each of the second electrodes **263a**, **263b**, and **263c** deposited on the photo-reactive organic film **280** of the organic light emitting layer **262** in accordance with an amount of UV irradiation. As the amount of UV irradiation is increased, the thickness of the second electrode deposited on the photo-reactive organic film **280** becomes thicker. Thus, the amount of UV irradiation applied to the third subpixel (P3) is the largest, and the amount of UV irradiation applied to the first subpixel (P1) is the smallest, whereby the thickness of the second electrode **263c** for the third subpixel (P3) is the largest, and the thickness of the second electrode **263a** for the first subpixel (P1) is the smallest, as shown in FIG. 13C. Due to the difference in the amount of UV irradiation between the first transmitting portion T1, the second transmitting portion T2, and the third transmitting portion T3, the hydrophobicity of a first portion of the photo-reactive organic film **280** below the second electrode **263a** of the first subpixel P1 may be larger than a hydrophobicity of a second portion of the photo-reactive organic film **280** below the second electrode **263b** of the second subpixel P2. The hydrophobicity of the second portion of the photo-reactive organic film **280** may be larger than a hydrophobicity of a third portion of the photo-reactive organic film **280** below the second electrode **263c** of the third subpixel P3. The hydrophobicity of the first portion, the second portion, and the third portion of the photo-reactive organic film **280** may be smaller than a portion of the photo-reactive organic film **280** that does not overlap with the second electrodes **263a**, **263b**, and **263c**.

As described above, the second electrode **263a** of the first subpixel (P1), the second electrode **263b** of the second subpixel (P2), and the second electrode **263c** of the third subpixel (P3) may have the different thicknesses from one another by adjusting the amount of UV irradiation applied to

the first to third subpixels (P1, P2, P3). Thus, it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3).

Fourth, as shown in FIG. 13D, the semi-transmissive electrode **290** and the encapsulation film **300** are provided on the photo-reactive organic film **280** of the organic light emitting layer **262**, and the second electrodes **263a**, **263b**, and **263c**, as indicated in S304 of FIG. 12.

The step S304 of FIG. 12 is the same as the step S104 of FIG. 6, whereby a detailed description for the step S304 of FIG. 12 will be omitted.

As described above, the electron transporting layer of the organic light emitting layer **262** is formed of the photoreactive organic film **280**, and the second electrode **263a** of the first subpixel (P1), the second electrode **263b** of the second subpixel (P2), and the second electrode **263c** of the third subpixel (P3) have the different thicknesses from one another by the use of first mask (M1) having transmitting portions (T1, T2, T3) with the different UV transmittances. As a result, it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3) by the two processes including the UV irradiation process, and deposition process of the metal film. Accordingly, it is possible to largely reduce the number of manufacturing processes, to simplify the manufacturing process, and to reduce a manufacturing cost.

FIG. 14 is a flow chart illustrating a method for manufacturing an OLED device according to another embodiment of the present disclosure. FIGS. 15A to 15H are cross sectional views illustrating the method for manufacturing the OLED device according to another embodiment of the present disclosure.

The cross sectional views shown in FIGS. 15A to 15H relate to the method for manufacturing the above OLED device shown in FIG. 10, whereby the same reference numbers will be used throughout the drawings to refer to the same or like parts. Hereinafter, the method for manufacturing the OLED device according to another embodiment of the present invention will be described in detail with reference to FIG. 14 and FIGS. 15A to 15H.

First, as shown in FIG. 15A, the thin film transistors **210**, anode electrodes **261**, and the organic light emitting layer **262** are provided, as indicated in S401 of FIG. 14.

The step S401 of FIG. 14 is the same as the step S301 of FIG. 12, whereby a detailed description for the step S401 of FIG. 14 will be omitted.

Second, as shown in FIGS. 15B and 15C, second electrodes **263c'** are formed by irradiating the area for the third subpixel (P3) with UV, as indicated in S402 of FIG. 14.

In detail, as shown in FIG. 15B, under the condition that a second mask (M2) having a transmitting portion (T) is disposed on the organic light emitting layer **262**, the organic light emitting layer **262** is irradiated with UV. In this case, the transmitting portion (T) is positioned in the area for the third subpixel (P3). The first and second subpixels (P1, P2) are not irradiated with UV, and only the third subpixel (P3) is irradiated with UV.

As shown in FIG. 5, the photo-reactive organic film **280** includes diarylethene molecules. Thus, the metal film is deposited only on the area of the photo-reactive organic film **280** which is irradiated with UV, and the metal film is not deposited on the area of the photo-reactive organic film **280** which is not irradiated with UV. Accordingly, even though an open mask having a transmitting portion for the display area is used instead of a mask having transmitting portions

for the third subpixel (P3), as shown in FIG. 15C, the second electrode 263c' may be deposited only on the third subpixel (P3).

Third, as shown in FIGS. 15D and 15E, the area for the second subpixel (P2) is irradiated with UV, to thereby form second electrodes 263b' and 263c", as indicated in S403 of FIG. 14.

In detail, as shown in FIG. 15D, under the condition that a third mask (M3) having a transmitting portion (T) is disposed on the organic light emitting layer 262, the organic light emitting layer 262 is irradiated with UV. In this case, the transmitting portion (T) is positioned in the area for the second subpixel (P2). The first and third subpixels (P1, P3) are not irradiated with UV, and only the second subpixel (P2) is irradiated with UV.

As shown in FIG. 5, the photo-reactive organic film 280 includes diarylethene molecules. Thus, the metal film is deposited only on the area of the photo-reactive organic film 280 which is irradiated with UV, and the metal film is not deposited on the area of the photo-reactive organic film 280 which is not irradiated with UV. Accordingly, even though an open mask having a transmitting portion for the display area is used instead of a mask having transmitting portions for the second and third subpixel (P2, P3), as shown in FIG. 15E, the second electrodes 263b' and 263c" may be deposited on the second and third subpixels (P2, P3) irradiated with UV.

Fourth, as shown in FIGS. 15F and 15G, the area for the first subpixel (P1) is irradiated with UV, to thereby form the second electrodes 263a, 263b, and 263c, as indicated in S404 of FIG. 14.

In detail, as shown in FIG. 15F, under the condition that a fourth mask (M4) having a transmitting portion (T) is disposed on the organic light emitting layer 262, the organic light emitting layer 262 is irradiated with UV. In this case, the transmitting portion (T) is positioned in the area for the first subpixel (P1). In this case, the second and third subpixels (P2, P3) are not irradiated with UV, and only the first subpixel (P1) is irradiated with UV.

As shown in FIG. 5, the photo-reactive organic film 280 includes diarylethene molecules. Thus, the metal film is deposited only on the area of the photo-reactive organic film 280 which is irradiated with UV, and the metal film is not deposited on the area of the photo-reactive organic film 280 which is not irradiated with UV. Accordingly, even though an open mask having a transmitting portion for the display area is used instead of a mask having transmitting portions for the first to third subpixels (P1, P2, P3), as shown in FIG. 15G, the second electrodes 263a, 263b, and 263c may be deposited on the first to third subpixels (P1, P2, P3) irradiated with UV. When the transmittance of the second mask M2, third mask M3, and the fourth mask M4 are substantially similar, a hydrophobicity of a first portion of the photo-reactive organic film 280 below the second electrode 263a of the first subpixel P1, a hydrophobicity of a second portion of the photo-reactive organic film 280 below the second electrode 263b of the second subpixel P2, and a hydrophobicity of a third portion of the photo-reactive organic film 280 below the second electrode 263c of the third subpixel P3 may be substantially same with one another. The hydrophobicity of the first portion, the second portion, and the third portion of the photo-reactive organic film 280 may be smaller than a portion of the photo-reactive organic film 280 that does not overlap with the second electrodes 263a, 263b, and 263c.

Meanwhile, the metal film is deposited on the photo-reactive organic film 280 of the third subpixel (P3) by the

steps of S402, S403, and S404, the metal film is deposited on the photo-reactive organic film 280 of the second subpixel (P2) by the steps of S403 and S404, and the metal film is deposited on the photo-reactive organic film 280 of the first subpixel (P1) by the steps of S404. Accordingly, the second electrode 263c of the third subpixel (P3) has the largest thickness, and the second electrode 263a of the first subpixel (P1) has the smallest thickness. That is, the thickness of the second electrode 263a for the first subpixel (P1), the thickness of the second electrode 263b for the second subpixel (P2), and the thickness of the second electrode 263c for the third subpixel (P3) may be different from one another.

Fifth, as shown in FIG. 15H, the semi-transmissive electrode 290 and the encapsulation film 300 are provided on the photo-reactive organic film 280, and the second electrodes 263a, 263b, and 263c, as indicated in S405 of FIG. 14.

The step S405 of FIG. 14 is the same as the step S104 of FIG. 6, whereby a detailed description for the step S405 of FIG. 14 will be omitted ('S405' of FIG. 14).

As described above, after the second electrode 263c' is deposited by irradiating the area for the third subpixel (P3) with UV, the second electrodes 263b' and 263c" are deposited by irradiating the area for the second subpixel (P2) with UV, and then the second electrodes 263a, 263b, and 263c are deposited by irradiating the area for the first subpixel (P1) with UV. As a result, the thickness of the second electrode 263a in the first subpixel (P1), the thickness of the second electrode 263b in the second subpixel (P2), and the thickness of the second electrode 263c in the third subpixel (P3) may be different from one another. As a result, it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3) by the six processes including three UV irradiation processes and three deposition processes of the metal film. Accordingly, it is possible to largely reduce the number of manufacturing processes, to simplify the manufacturing process, and to reduce a manufacturing cost.

According to the present disclosure, the first electrode 261 is formed of the metal material with high reflectance, and the semi-transmissive electrode 290 is formed of the semi-transmissive metal material, whereby it is possible to realize the micro-cavity structure by the first electrode 261 and the semi-transmissive electrode 290, to thereby improve the emission efficiency of light emitted from the organic light emitting layer 262.

Also, the first optical auxiliary layer 281 of the first subpixel (P1), the second optical auxiliary layer 282 of the second subpixel (P2), and the third optical auxiliary layer 283 of the third subpixel (P3) have the different thicknesses from one another, whereby it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3).

Accordingly, the deposition process of the photo-reactive organic film 280, the UV irradiation process, and the deposition process of the metal film are additionally carried out so that the first optical auxiliary layer 281 of the first subpixel (P1), the second optical auxiliary layer 282 of the second subpixel (P2), and the third optical auxiliary layer 283 of the third subpixel (P3) have the different thicknesses from one another. Thus, it is possible to largely reduce the number of manufacturing processes, to thereby simplify the manufacturing process, and to reduce the manufacturing cost.

According to the embodiment of the present invention, the second electrode 263a of the first subpixel (P1), the second electrode 263b of the second subpixel (P2), and the second electrode 263c of the third subpixel (P3) have the

different thicknesses from one another by adjusting the amount of UV irradiation applied to the first to third subpixels (P1, P2, P3), whereby it is possible to optimize the micro-cavity distance in each of the first to third subpixels (P1, P2, P3).

Furthermore, the deposition process of the photo-reactive organic film 280, the UV irradiation process, and the deposition process of the metal film are additionally carried out so that the second electrode 263a of the first subpixel (P1), the second electrode 263b of the second subpixel (P2), and the second electrode 263c of the third subpixel (P3) have the different thicknesses from one another. Thus, it is possible to largely reduce the number of manufacturing processes, to thereby simplify the manufacturing process, and to reduce the manufacturing cost.

It will be apparent to those skilled in the art that various modifications and variations can be made in the present invention without departing from the spirit or scope of the inventions. Thus, it is intended that the present invention covers the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An organic light emitting display (OLED) device comprising a pixel having a first subpixel, a second subpixel, and a third subpixel, wherein each of the first subpixel, the second subpixel, and the third subpixel includes:
 - a first electrode including a reflective metal material, an organic light emitting layer disposed on the first electrode,
 - a second electrode disposed on the organic light emitting layer and formed of a transparent metal material, a photo-reactive organic film disposed on the second electrode, and
 - a semi-transmissive electrode disposed on the photo-reactive organic film,
 wherein a first distance between the first electrode and the semi-transmissive electrode of the first subpixel, a second distance between the first electrode and the semi-transmissive electrode of the second subpixel, and a third distance between the first electrode and the semi-transmissive electrode of the third subpixel are different from one another, wherein the first subpixel further includes a first optical auxiliary layer disposed between a first part of the photo-reactive organic film and the semi-transmissive electrode, and wherein the second subpixel further includes a second optical auxiliary layer disposed on a second part of the photo-reactive organic film and the semi-transmissive electrode.
2. The OLED device according to claim 1, further comprising:
 - a third optical auxiliary layer disposed between a third part of the photo-reactive organic film and the semi-transmissive electrode.
3. The OLED device according to claim 2, wherein the photo-reactive organic film includes diarylethene molecules.
4. The OLED device according to claim 3, wherein a thickness of the first optical auxiliary layer, a thickness of the second optical auxiliary layer, and a thickness of the third optical auxiliary layer are different from one another.
5. The OLED device according to claim 2, wherein the semi-transmissive electrode of the first subpixel is disposed on the first optical auxiliary layer, wherein the semi-transmissive electrode of the second subpixel is disposed on the

second optical auxiliary layer, and the semi-transmissive electrode of the third subpixel is disposed on the third optical auxiliary layer.

6. An organic light emitting display (OLED) device comprising a pixel having a first subpixel, a second subpixel, and a third subpixel, wherein each of the first subpixel, the second subpixel, and the third subpixel includes:

- a first electrode including a reflective metal material,
- a light emitting layer disposed on the first electrode,
- a photo-reactive organic film disposed on the light emitting layer,
- a second electrode disposed on the photo-reactive organic film and formed of a transparent metal material, and
- a semi-transmissive electrode disposed on the second electrode,

wherein a thickness of the second electrode in the first subpixel, a thickness of the second electrode in the second subpixel, and a thickness of the second electrode in the third subpixel are different from one another.

7. The OLED device according to claim 6, wherein the photo-reactive organic film includes diarylethene molecules.

8. The OLED device according to claim 6, wherein the photo-reactive organic film has an electron transporting capacity.

9. A light emitting display device, comprising:

- a substrate;
- a first subpixel on the substrate, the first subpixel including:
 - a first bottom electrode,
 - at least a first part of an organic light emitting layer on the first bottom electrode,
 - a first conductive film on the first part of the organic light emitting layer, and
 - at least a first part of a semi-transmissive electrode on the first conductive film; and
- a second subpixel on the substrate, the second subpixel including:
 - a second bottom electrode,
 - at least a second part of the organic light emitting layer on the second bottom electrode,
 - a second conductive film on the second part of the organic light emitting layer, and
 - at least a second part of the semi-transmissive electrode on the second conductive film,
 wherein a thickness of the second conductive film is greater than a thickness of the first conductive film.

10. The light emitting display device of claim 9, further comprising an organic film disposed below the first conductive film and the second conductive film, wherein a hydrophobicity of a first portion of the organic film below the first conductive film is larger than a hydrophobicity of a second portion of the organic film below the second conductive film, and wherein the hydrophobicity of the first portion and the second portion of the organic film is smaller than a hydrophobicity of a third portion of the organic film that does not overlap with the first conductive film or the second conductive film.

11. The light emitting display device of claim 9, further comprising an organic film disposed below the first conductive film and the second conductive film, wherein a hydrophobicity of a first portion of the organic film below the first conductive film is substantially same as a hydrophobicity of a second portion of the organic film below the second conductive film, and wherein the hydrophobicity of the first portion and the second portion of the organic film is smaller

31

than a hydrophobicity of a third portion of the organic film that does not overlap with the first conductive film or the second conductive film.

12. The light emitting display device of claim 9, further comprising an upper electrode disposed between the first conductive film and the first part of the organic light emitting layer, and disposed between the second conductive film and the second part of the organic light emitting layer.

13. The light emitting display device of claim 12, further comprising a photo-reactive organic film disposed between the first conductive film and the upper electrode, and disposed between the second conductive film and the upper electrode.

14. The light emitting display device of claim 9, wherein the first conductive film is a first cathode electrode of the first subpixel and the second conductive film is a second cathode electrode of the second subpixel.

15. The light emitting display device of claim 14, wherein the organic light emitting layer includes a photo-reactive organic film, and wherein the photo-reactive organic film is in contact with the first conductive film and the second conductive film.

16. The light emitting display device of claim 9, further comprising a photo-reactive film organic disposed below the

32

first conductive film and the second conductive film, wherein the photo-reactive organic film includes diarylethene molecules.

17. The light emitting display device of claim 9, further comprising:

a third subpixel on the substrate, the third subpixel including:

a third bottom electrode,

at least a third part of the organic light emitting layer on the third bottom electrode,

a third conductive film on the third part of the organic light emitting layer, and

at least a third part of the semi-transmissive electrode on the third conductive film,

wherein a thickness of the third conductive film is greater than the thickness of the second conductive film.

18. The light emitting display device of claim 9, wherein the first conductive film and the second conductive film are formed of a transparent conductive oxide material.

19. The light emitting display device of claim 9, wherein the semi-transmissive electrode includes at least one of magnesium (Mg), argentum (Ag), or an alloy of magnesium (Mg) and argentum (Ag).

* * * * *

专利名称(译)	有机发光显示装置及其制造方法		
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[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	PARK TAEHAN LEE KYUNGHOON YOO DONGHEE LIM HYEONGJUN		
发明人	PARK, TAEHAN LEE, KYUNGHOON YOO, DONGHEE LIM, HYEONGJUN		
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摘要(译)

公开了一种能够减少应用微腔结构的制造工艺的数量的OLED器件及其制造方法，其中OLED器件可以包括具有第一至第三子像素的像素，其中第一至第三子像素中的每一个子像素包括：第一电极，包括反射金属材料；第一电极，第一电极上的有机发光层；第二电极，设置在有机发光层上，由透明金属材料形成；以及半透射电极，位于第二电极上，其中第一子电极中的第一电极和半透射电极之间的距离，第二子像素中的第一电极和半透射电极之间的距离，以及第一电极和半透射电极之间的距离第三子像素彼此不同。

